

GigaDevice Semiconductor Inc.

GD32E230xx ARM® Cortex®-M23 32-bit MCU

Datasheet

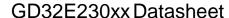


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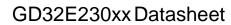




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1 General description

The GD32E230xx device belongs to the value line of GD32 MCU family. It is a new 32-bit general-purpose microcontroller based on the ARM® Cortex®-M23 core. The Cortex-M23 processor is an energy-efficient processor with a very low gate count. It is intended to be used for microcontroller and deeply embedded applications that require an area-optimized processor. The processor delivers high energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier and a 17-cycle divider.

The GD32E230xx device incorporates the ARM® Cortex®-M23 32-bit processor core operating at up to 72 MHz frequency with Flash accesses 0~2 wait states to obtain maximum efficiency. It provides up to 64 KB embedded Flash memory and up to 8 KB SRAM memory. An extensive range of enhanced I/Os and peripherals connected to two APB buses. The devices offer one 12-bit ADC and one comparator, up to five general 16-bit timers, a basic timer, a PWM advanced timer, as well as standard and advanced communication interfaces: up to two SPIs, two I2Cs, two USARTs, and an I2S.

The device operates from a 1.8 to 3.6 V power supply and available in -40 to +85 °C temperature range. Several power saving modes provide the flexibility for maximum optimization between wakeup latency and power consumption, an especially important consideration in low power applications.

The above features make the GD32E230xx devices suitable for a wide range of applications, especially in areas such as industrial control, motor drives, user interface, power monitor and alarm systems, consumer and handheld equipment, gaming and GPS, E-bike and so on.





2 Device overview

2.1 Device information

Table 2-1. GD32E230xx devices features and peripheral list

						D32E230				
		K4U6	K6U6	K8U6	K4T6	K6T6	K8T6	C4T6	C6T6	C8T6
F	LASH (KB)	16	32	64	16	32	64	16	32	64
5	SRAM (KB)	4	6	8	4	4	8	4	6	8
	General	4	4	5	4	4	5	4	4	5
	timer(16-bit)	(2,13,15,16)	(2,13,15,16)	(2,13-16)	(2,13,15,16)	(2,13,15,16)	(2,13-16)	(2,13,15,16)	(2,13,15,16)	(2,13-16)
	Advanced	1	1	1	1	1	1	1	1	1
S	timer(16-bit)	(0)	(0)	(0)	(0)	(0)	(0)	(0)	(0)	(0)
mer	Advanced timer(16-bit) SysTick Basic	1	1	1	1	1	1	1	1	1
Ξ	Basic	1	1	1	1	1	1	1	1	1
	timer(16-bit)	(5)	(5)	(5)	(5)	(5)	(5)	(5)	(5)	(5)
	Watchdog	2	2	2	2	2	2	2	2	2
	RTC	1	1	1	1	1	1	1	1	1
	USART	1	2	2	1	2	2	1	2	2
/ity		(0)	(0-1)	(0-1)	(0)	(0-1)	(0-1)	(0)	(0-1)	(0-1)
cti	I2C	1	1	2	1	1	2	1	1	2
Connectivity	120	(0)	(0)	(0-1)	(0)	(0)	(0-1)	(0)	(0)	(0-1)
Co	SPI/I2S	1/1	1/1	2/1	1/1	1/1	2/1	1/1	1/1	2/1
		(0)/(0)	(0)/(0)	(0-1)/(0)	(0)/(0)	(0)/(0)	(0-1)/(0)	(0)/(0)	(0)/(0)	(0-1)/(0)
	GPIO	27	27	27	25	25	25	39	39	39
	CMP	1	1	1	1	1	1	1	1	1
	EXTI	16	16	16	16	16	16	16	16	16
	Units	1	1	1	1	1	1	1	1	1
	Channels	10	10	10	10	10	10	10	10	10
ADC	(External)	10	10	10	10	10	10	10	10	10
	Channels	2	2	2	2	2	2	2	2	2
	(Internal)									~
	Package		QFN32			LQFP32			LQFP48	



Table 2-2. GD32E230xx devices features and peripheral list (continued)

FLASH (KB)						D32E230		(00	,	
		F4U6	F6U6	F8U6	F4P6	F6P6	F8P6	G4U6	G6U6	G8U6
		16	32	64	16	32	64	16	32	64
SRAM (KB)		4	6	8	4	6	8	4	6	8
	General	4	4	4	4	4	4	4	4	5
	timer(16-bit)	(2,13,15,16)	(2,13,15,16)	(2,13,15,16)	(2,13,15,16)	(2,13,15,16)	(2,13,15,16)	(2,13,15,16)	(2,13,15,16)	(2,13-16)
	Advanced	1	1	1	1	1	1	1	1	1
"	timer(16-bit)	(0)	(0)	(0)	(0)	(0)	(0)	(0)	(0)	(0)
Timers	SysTick	1	1	1	1	1	1	1	1	1
ļ≓	Basic	1	1	1	1	1	1	1	1	1
	timer(16-bit)	(5)	(5)	(5)	(5)	(5)	(5)	(5)	(5)	(5)
	Watchdog	2	2	2	2	2	2	2	2	2
	RTC	1	1	1	1	1	1	1	1	1
	USART	1	2	2	1	2	2	1	2	2
/ity		(0)	(0-1)	(0-1)	(0)	(0-1)	(0-1)	(0)	(0-1)	(0-1)
Connectivity	I2C	1	1	2	1	1	2	1	1	2
nne	120	(0)	(0)	(0-1)	(0)	(0)	(0-1)	(0)	(0)	(0-1)
ပိ	SPI/I2S	1/1	1/1	2/1	1/1	1/1	2/1	1/1	1/1	2/1
	01 1/120	(0)/(0)	(0)/(0)	(0-1)/(0)	(0)/(0)	(0)/(0)	(0-1)/(0)	(0)/(0)	(0)/(0)	(0-1)/(0)
	GPIO	15	15	15	15	15	15	23	23	23
	CMP	1	1	1	1	1	1	1	1	1
	EXTI	16	16	16	16	16	16	16	16	16
	Units	1	1	1	1	1	1	1	1	1
ADC	Channels (External)	9	9	9	9	9	9	10	10	10
	Channels (Internal)	2	2	2	2	2	2	2	2	2
	Package		QFN20		Т	SSOP20)		QFN28	

TIMER13



2.2 Block diagram

LDO 1.2V TPIU SW GPIO Ports AHB2: Fmax = 72MHz POR/PDR A, B, C, FARM Cortex-M23 AHB BUS Processor SRAM Controller LVD Fmax: 72MHz SRAM AHB Matrix PLL Fmax: 72MHz Flash Flash Memory NVIC Memory Controller HXTAL 4-32MHz GP DMA AHB1: Fmax = 72MHz IRC8M 介 钦 8MHz AHB to APB AHB to APB IRC28M RST/CLK Controller CRC Bridge 2 Bridge 1 28MHz IRC40K 40KHz Powered by LDO (1.2V) PMU EXTI FWDGT Powered by VDD/VDDA 12-bit ADC SAR ADC WWDGT RTC USART0 I2C0 SPI0/I2S0 I2C1 SYS Config CMP CMP USART1 SPI1 72MHz TIMER0 TIMER5 TIMER14 TIMER2 TIMER15

TIMER16

Figure 2-1. GD32E230xx block diagram



2.3 Pinouts and pin assignment

Figure 2-2. GD32E230Cx LQFP48 pinouts

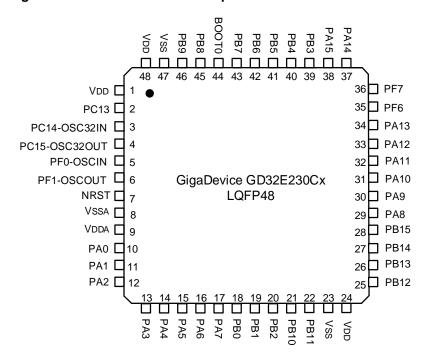


Figure 2-3. GD32E230Kx LQFP32 pinouts

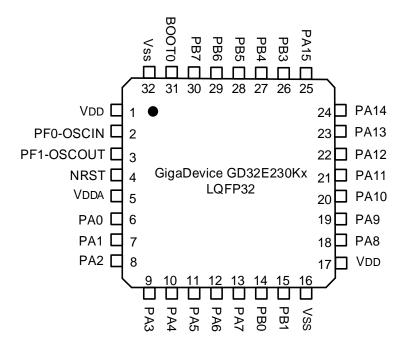




Figure 2-4. GD32E230Kx QFN32 pinouts

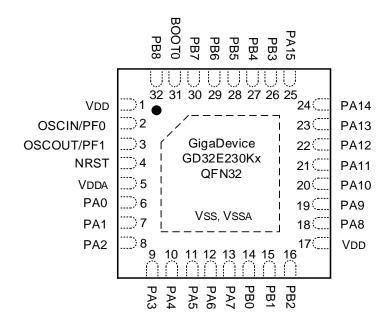


Figure 2-5. GD32E230Gx QFN28 pinouts

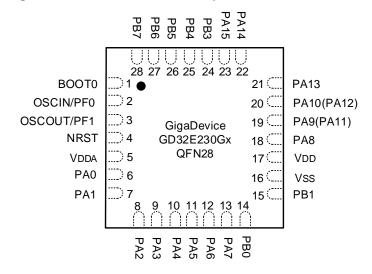


Figure 2-6. GD32E230Fx TSSOP20 pinouts

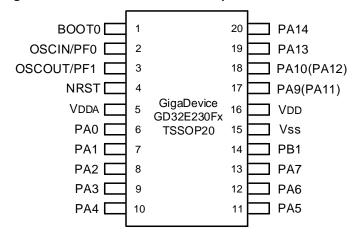
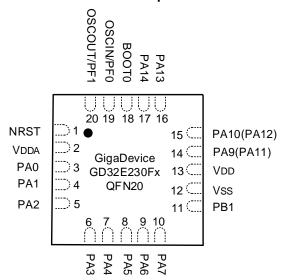




Figure 2-7. GD32E230Fx QFN20 pinouts

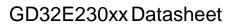




2.4 Memory map

Table 2-3. GD32E230xx memory map

Pre-defined Bus		ADDDECO	Davida kanada		
Regions	Bus	ADDRESS	Peripherals		
		0xE000 0000 - 0xE00F FFFF	Cortex M23 internal peripherals		
External Device		0xA000 0000 - 0xDFFF FFFF	Reserved		
External RAM		0x60000000 - 0x9FFFFFF	Reserved		
	ALID4	0x5004 0000 - 0x5FFF FFFF	Reserved		
	AHB1	0x5000 0000 - 0x5003 FFFF	Reserved		
		0x4800 1800 - 0x4FFF FFFF	Reserved		
		0x4800 1400 - 0x4800 17FF	GPIOF		
		0x4800 1000 - 0x4800 13FF	Reserved		
	AHB2	0x4800 0C00 - 0x4800 0FFF	Reserved		
		0x4800 0800 - 0x4800 0BFF	GPIOC		
		0x4800 0400 - 0x4800 07FF	GPIOB		
		0x4800 0000 - 0x4800 03FF	GPIOA		
		0x4002 4400 - 0x47FF FFFF	Reserved		
		0x4002 4000 - 0x4002 43FF	Reserved		
		0x4002 3400 - 0x4002 3FFF	Reserved		
	AHB1	0x4002 3000 - 0x4002 33FF	CRC		
		0x4002 2400 - 0x4002 2FFF	Reserved		
		0x4002 2000 - 0x4002 23FF	FMC		
		0x4002 1400 - 0x4002 1FFF	Reserved		
5		0x4002 1000 - 0x4002 13FF	RCU		
Peripherals		0x4002 0400 - 0x4002 0FFF	Reserved		
		0x4002 0000 - 0x4002 03FF	DMA		
		0x4001 8000 - 0x4001 FFFF	Reserved		
		0x4001 5C00 - 0x4001 7FFF	Reserved		
		0x4001 5800 - 0x4001 5BFF	DBG		
		0x4001 4C00 - 0x4001 57FF	Reserved		
		0x4001 4800 - 0x4001 4BFF	TIMER16		
		0x4001 4400 - 0x4001 47FF	TIMER15		
		0x4001 4000 - 0x4001 43FF	TIMER14		
	APB2	0x4001 3C00 - 0x4001 3FFF	Reserved		
		0x4001 3800 - 0x4001 3BFF	USART0		
		0x4001 3400 - 0x4001 37FF	Reserved		
		0x4001 3000 - 0x4001 33FF	SPI0/I2S0		
		0x4001 2C00 - 0x4001 2FFF	TIMER0		
		0x4001 2800 - 0x4001 2BFF	Reserved		
		0x4001 2400 - 0x4001 27FF	ADC		
		0x4001 0800 - 0x4001 23FF	Reserved		





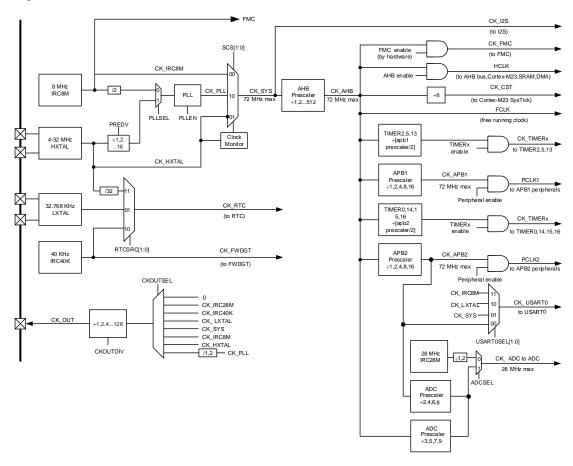
Pre-defined Bus		ADDRESS	Peripherals
Regions		0.4004 0400 0.4004 0755	EVT.
		0x4001 0400 - 0x4001 07FF	EXTI
		0x4001 0000 - 0x4001 03FF	SYSCFG + CMP
		0x4000 CC00 - 0x4000 FFFF	Reserved
		0x4000 C800 - 0x4000 CBFF	Reserved
		0x4000 C400 - 0x4000 C7FF	Reserved
		0x4000 C000 - 0x4000 C3FF	Reserved
		0x4000 8000 - 0x4000 BFFF	Reserved
		0x4000 7C00 - 0x4000 7FFF	Reserved
		0x4000 7800 - 0x4000 7BFF	Reserved
		0x4000 7400 - 0x4000 77FF	Reserved
		0x4000 7000 - 0x4000 73FF	PMU
		0x4000 6400 - 0x4000 6FFF	Reserved
		0x4000 6000 - 0x4000 63FF	Reserved
		0x4000 5C00 - 0x4000 5FFF	Reserved
		0x4000 5800 - 0x4000 5BFF	I2C1
		0x4000 5400 - 0x4000 57FF	I2C0
		0x4000 4800 - 0x4000 53FF	Reserved
	APB1	0x4000 4400 - 0x4000 47FF	USART1
		0x4000 4000 - 0x4000 43FF	Reserved
		0x4000 3C00 - 0x4000 3FFF	Reserved
		0x4000 3800 - 0x4000 3BFF	SPI1
		0x4000 3400 - 0x4000 37FF	Reserved
		0x4000 3000 - 0x4000 33FF	FWDGT
		0x4000 2C00 - 0x4000 2FFF	WWDGT
		0x4000 2800 - 0x4000 2BFF	RTC
		0x4000 2400 - 0x4000 27FF	Reserved
		0x4000 2000 - 0x4000 23FF	TIMER13
		0x4000 1400 - 0x4000 1FFF	Reserved
		0x4000 1000 - 0x4000 13FF	TIMER5
		0x4000 0800 - 0x4000 0FFF	Reserved
		0x4000 0400 - 0x4000 07FF	TIMER2
		0x4000 0000 - 0x4000 03FF	Reserved
		0x2000 2000 - 0x3FFF FFFF	Reserved
SRAM		0x2000 0000 - 0x2000 1FFF	SRAM
		0x1FFF F810 - 0x1FFF FFFF	Reserved
		0x1FFF F800 - 0x1FFF F80F	Option bytes
		0x1FFF EC00 - 0x1FFF F7FF	System memory
Code		0x0801 0000 - 0x1FFF EBFF	Reserved
		0x0800 0000 - 0x0800 FFFF	Main Flash memory
		0x0001 0000 - 0x07FF FFFF	Reserved



Pre-defined Regions	Bus	ADDRESS	Peripherals	
		0x00000000 - 0x0000FFFF	Aliased to Flash or	
		0.00000000 - 0.00000FFFF	system memory	

2.5 Clock tree

Figure 2-8. GD32E230xx clock tree



Note:

If the APB prescaler is 1, the timer clock frequencies are set to AHB frequency divide by 1. Otherwise, they are set to the AHB frequency divide by half of APB prescaler.

Legend:

HXTAL: High speed crystal oscillator LXTAL: Low speed crystal oscillator IRC8M: Internal 8M RC oscillator IRC40K: Internal 40K RC oscillator IRC28M: Internal 28M RC oscillator

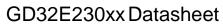


2.6 Pin definitions

2.6.1 GD32E230Cx LQFP48 pin definitions

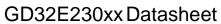
Table 2-4. GD32E230Cx LQFP48 pin definitions

Pin Name Pins Pin I/O Functions descri		E-mariana da animia			
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description	
V_{DD}	1	Р		Default: V _{DD}	
PC13- TAMPER- RTC	2	I/O		Default: PC13 Additional: RTC_TAMP0, RTC_TS, RTC_OUT, WKUP1	
PC14- OSC32IN	3	I/O		Default: PC14 Additional: OSC32IN	
PC15- OSC32OUT	4	I/O		Default: PC15 Additional: OSC32OUT	
PF0-OSCIN	5	I/O	5VT	Default: PF0 Alternate: I2C0_SDA Additional: OSCIN	
PF1- OSCOUT	6	I/O	5VT	Default: PF1 Alternate: I2C0_SCL Additional: OSCOUT	
NRST	7	I/O		Default: NRST	
Vssa	8	Р		Default: V _{SSA}	
V_{DDA}	9	Р		Default: V _{DDA}	
PA0-WKUP	10	I/O		Default: PA0 Alternate: USART0_CTS ⁽³⁾ , USART1_CTS ⁽⁴⁾ , CMP_OUT, I2C1_SCL ⁽⁵⁾ Additional: ADC_IN0, CMP_IM6, RTC_TAMP1, WKUP0	
PA1	11	I/O		Default: PA1 Alternate: USART0_RTS ⁽³⁾ , USART1_RTS ⁽⁴⁾ , I2C1_SDA ⁽⁵⁾ , EVENTOUT, TIMER14_CH0_ON ⁽⁵⁾ Additional: ADC_IN1, CMP_IP	
PA2	12	I/O		Default: PA2 Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , TIMER14_CH0 ⁽⁵⁾ Additional: ADC_IN2, CMP_IM7	
PA3	13	I/O		Default: PA3 Alternate: USART0_RX ⁽³⁾ , USART1_RX ⁽⁴⁾ , TIMER14_CH1 ⁽⁵⁾ Additional: ADC_IN3	
PA4	14	I/O		Default: PA4 Alternate: SPI0_NSS, I2S0_WS, USART0_CK ⁽³⁾ , USART1_CK ⁽⁴⁾ , TIMER13_CH0, SPI1_NSS ⁽⁵⁾ Additional: ADC_IN4, CMP_IM4	





ī				ODJZEZJOAA Datasi iee		
	Pin Name	Pins	Pin	1/0	Functions description	
			Type ⁽¹⁾	Level ⁽²⁾	·	
					Default: PA5	
	PA5	15	I/O		Alternate: SPI0_SCK, I2S0_CK	
ļ					Additional: ADC_IN5, CMP_IM5	
					Default: PA6	
					Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,	
	PA6	16	I/O		TIMER0_BRKIN, TIMER15_CH0, EVENTOUT,	
					CMP_OUT	
ļ					Additional: ADC_IN6	
					Default: PA7	
					Alternate: SPI0_MOSI, I2S0_SD, TIMER2_CH1,	
	PA7	17	I/O		TIMER13_CH0, TIMER0_CH0_ON, TIMER16_CH0,	
					EVENTOUT	
ļ					Additional: ADC_IN7	
					Default: PB0	
	PB0	18	I/O		Alternate: TIMER2_CH2, TIMER0_CH1_ON,	
					USART1_RX ⁽⁴⁾ , EVENTOUT	
ļ					Additional: ADC_IN8	
					Default: PB1	
	PB1	19	I/O		Alternate: TIMER2_CH3, TIMER13_CH0,	
					TIMER0_CH2_ON, SPI1_SCK ⁽⁵⁾	
ļ					Additional: ADC_IN9	
	PB2	20	I/O	5VT	Default: PB2	
ļ					Alternate: TIMER2_ETI	
	DD 40	0.4	1/0	E) /T	Default: PB10	
	PB10	21	I/O	5VT	Alternate: I2C0_SCL ⁽³⁾ ,I2C1_SCL ⁽⁵⁾ , SPI1_IO2 ⁽⁵⁾ ,	
ŀ					SPI1_SCK ⁽⁵⁾ Default: PB11	
	PB11	22	I/O	5VT	Alternate: I2C0_SDA ⁽³⁾ ,I2C1_SDA ⁽⁵⁾ , EVENTOUT,	
	PDII	22	1/0	371	SPI1_IO3 ⁽⁵⁾	
ŀ	\/	22	Р		Default: V _{SS}	
ŀ	V _{SS}	23				
ŀ	V _{DD}	24	Р		Default: V _{DD}	
					Default: PB12	
	PB12	25	I/O	5VT	Alternate: SPI0_NSS ⁽³⁾ , SPI1_NSS ⁽⁵⁾ , TIMER0_BRKIN,	
ļ					I2C1_SMBA ⁽⁵⁾ , EVENTOUT	
					Default: PB13	
	PB13	26	I/O	5VT	Alternate: SPI0_SCK ⁽³⁾ , SPI1_SCK ⁽⁵⁾ , TIMER0_CH0_ON,	
					I2C1_TXFRAME ⁽⁵⁾ , I2C1_SCL ⁽⁵⁾	
					Default: PB14	
	PB14	27	I/O	5VT	Alternate: SPI0_MISO ⁽³⁾ , SPI1_MISO ⁽⁵⁾ ,	
					TIMER0_CH1_ON, TIMER14_CH0 ⁽⁵⁾ , I2C1_SDA ⁽⁵⁾	
					Default: PB15	
					Alternate: SPI0_MOSI ⁽³⁾ , SPI1_MOSI ⁽⁵⁾ ,	
	PB15	28	I/O	5VT	TIMER0_CH2_ON, TIMER14_CH0_ON ⁽⁵⁾ ,	
					TIMER14_CH1 ⁽⁵⁾	
					Additional: RTC_REFIN, WKUP6	
L						





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	Pin Name	Pins	Pin	I/O	Functions description	
			Type ⁽¹⁾	Level ⁽²⁾	•	
					Default: PA8	
	PA8	29	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT,	
_					USART1_TX ⁽⁴⁾ , EVENTOUT	
					Default: PA9	
	PA9	30	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1,	
-					TIMER14_BRKIN ⁽⁵⁾ , I2C0_SCL, CK_OUT	
					Default: PA10	
	PA10	31	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2,	
					TIMER16_BRKIN, I2C0_SDA	
					Default: PA11	
	PA11	32	I/O	5VT	Alternate: USART0_CTS, TIMER0_CH3, CMP_OUT,	
_					EVENTOUT, SPI1_IO2 ⁽⁵⁾ , I2C0_SMBA, I2C1_SCL ⁽⁵⁾	
					Default: PA12	
	PA12	33	I/O	5VT	Alternate: USART0_RTS, TIMER0_ETI, EVENTOUT,	
L					SPI1_IO3 ⁽⁵⁾ , I2C0_TXFRAME, I2C1_SDA ⁽⁵⁾	
	PA13	34	I/O	5VT	Default: PA13	
_		_		_	Alternate: SWDIO, IFRP_OUT, SPI1_MISO ⁽⁵⁾	
	PF6	35	I/O	5VT	Default: PF6	
-					Alternate: I2C0_SCL ⁽³⁾ , I2C1_SCL ⁽⁵⁾	
	PF7	36	I/O	5VT	Default: PF7	
-					Alternate: I2C0_SDA ⁽³⁾ , I2C1_SDA ⁽⁵⁾	
	5444	07	1/0	=\ (T	Default: PA14	
	PA14	37	I/O	5VT	Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , SWCLK,	
-					SPI1_MOSI ⁽⁵⁾ Default: PA15	
	DA4 <i>E</i>	38	I/O	5VT	Alternate: SPI0_NSS, I2S0_WS, USART0_RX ⁽³⁾ ,	
	PA15	30	1/0	371	USART1_RX ⁽⁴⁾ , SPI1_NSS ⁽⁵⁾ , EVENTOUT	
-					Default: PB3	
	PB3	39	I/O	5VT	Alternate: SPI0_SCK, I2S0_CK, EVENTOUT	
-					Default: PB4	
	PB4	40	I/O	5VT	Alternate: SPI0 MISO, I2S0 MCK, TIMER2 CH0,	
	1 54	40	1,0	371	EVENTOUT, I2C0_TXFRAME, TIMER16_BRKIN	
-					Default: PB5	
					Alternate: SPI0_MOSI,I2S0_SD, I2C0_SMBA,	
	PB5	41	I/O	5VT	TIMER15_BRKIN, TIMER2_CH1	
					Additional: WKUP5	
ŀ					Default: PB6	
	PB6	42	I/O	5VT	Alternate: I2C0_SCL, USART0_TX, TIMER15_CH0_ON	
				_,	Default: PB7	
	PB7	43	I/O	5VT	Alternate:I2C0_SDA, USART0_RX,TIMER16_CH0_ON	
	воото	44	I		Default: BOOT0	
j	DDC	4-	1/0	E) /=	Default: PB8	
	PB8	45	I/O	5VT	Alternate: I2C0_SCL, TIMER15_CH0	
ſ	D.C	4-	1/0	-> :	Default: PB9	
	PB9	46	I/O	5VT	Alternate: I2C0_SDA, IFRP_OUT, TIMER16_CH0,	
L				l	<u> </u>	



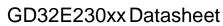
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				EVENTOUT, I2S0_MCK, SPI1_NSS ⁽⁵⁾
V_{SS}	47	Р		Default: V _{SS}
V_{DD}	48	Р		Default: V _{DD}

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Functions are available on GD32E230C4 devices only.
- (4) Functions are available on GD32E230C8/6 devices.
- (5) Functions are available on GD32E230C8 devices only.

2.6.2 GD32E230Kx LQFP32 pin definitions

Table 2-5. GD32E230Kx LQFP32 pin definitions

Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V_{DD}	1	Р		Default: V _{DD}
				Default: PF0
PF0-OSCIN	2	I/O	5VT	Alternate: I2C0_SDA
				Additional: OSCIN
PF1-				Default: PF1
	3	I/O	5VT	Alternate: I2C0_SCL
OSCOUT				Additional: OSCOUT
NRST	4	I/O		Default: NRST
V_{DDA}	5	Р		Default: V _{DDA}
				Default: PA0
DA O MUCUID	6	I/O		Alternate: USART0_CTS(3), USART1_CTS(4), CMP_OUT,
PA0-WKUP				I2C1_SCL ⁽⁵⁾
				Additional: ADC_IN0, CMP_IM6, RTC_TAMP1, WKUP0
	7	I/O		Default: PA1
PA1				Alternate: USART0_RTS ⁽³⁾ , USART1_RTS ⁽⁴⁾ ,
PAI				I2C1_SDA ⁽⁵⁾ , EVENTOUT, TIMER14_CH0_ON ⁽⁵⁾
				Additional: ADC_IN1, CMP_IP
				Default: PA2
PA2	8	I/O		Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ ,
FAZ				TIMER14_CH0 ⁽⁵⁾
				Additional: ADC_IN2, CMP_IM7
				Default: PA3
PA3	9	I/O		Alternate: USART0_RX ⁽³⁾ , USART1_RX ⁽⁴⁾ ,
1 73	9	1/0		TIMER14_CH1 ⁽⁵⁾
				Additional: ADC_IN3
				Default: PA4
PA4	10	I/O		Alternate: SPI0_NSS, I2S0_WS, USART0_CK ⁽³⁾ ,
				USART1_CK ⁽⁴⁾ , TIMER13_CH0, SPI1_NSS ⁽⁵⁾





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Pin Name	Pins	Pin	1/0	Functions description	
		Type ⁽¹⁾	Level ⁽²⁾	•	
				Additional: ADC_IN4, CMP_IM4	
				Default: PA5	
PA5	11	I/O		Alternate: SPI0_SCK, I2S0_CK	
				Additional: ADC_IN5, CMP_IM5	
				Default: PA6	
				Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,	
PA6	12	I/O		TIMER0_BRKIN, TIMER15_CH0, EVENTOUT,	
				CMP_OUT	
				Additional: ADC_IN6	
				Default: PA7	
				Alternate: SPI0_MOSI, I2S0_SD, TIMER2_CH1,	
PA7	13	I/O		TIMER13_CH0, TIMER0_CH0_ON, TIMER16_CH0,	
				EVENTOUT	
				Additional: ADC_IN7	
				Default: PB0	
PB0	14	I/O		Alternate: TIMER2_CH2, TIMER0_CH1_ON,	
1 60	14	1/0		USART1_RX ⁽⁴⁾ , EVENTOUT	
				Additional: ADC_IN8	
				Default: PB1	
PB1	15	I/O		Alternate: TIMER2_CH3, TIMER13_CH0,	
PDI	15	1/0		TIMER0_CH2_ON, SPI1_SCK ⁽⁵⁾	
				Additional: ADC_IN9	
Vss	16	Р		Default: V _{SS}	
V_{DD}	17	Р		Default: V _{DD}	
				Default: PA8	
PA8	18	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT,	
				USART1_TX ⁽⁴⁾ , EVENTOUT	
				Default: PA9	
PA9	19	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1,	
				TIMER14_BRKIN ⁽⁵⁾ , I2C0_SCL, CK_OUT	
				Default: PA10	
PA10	20	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2,	
				TIMER16_BRKIN, I2C0_SDA	
				Default: PA11	
PA11	21	I/O	5VT	Alternate: USART0_CTS, TIMER0_CH3, CMP_OUT,	
17(11	21	., 0	371	EVENTOUT, SPI1_IO2 ⁽⁵⁾ , I2C0_SMBA, I2C1_SCL ⁽⁵⁾	
				Default: PA12	
PA12	22	I/O	5VT	Alternate: USARTO_RTS, TIMERO_ETI, EVENTOUT,	
17112		"	J V I	SPI1_IO3 ⁽⁵⁾ , I2C0_TXFRAME, I2C1_SDA ⁽⁵⁾	
				Default: PA13	
PA13	23	I/O	5VT	Alternate: SWDIO, IFRP_OUT, SPI1_MISO ⁽⁵⁾	
				Default: PA14	
PA14	24	I/O	5VT	Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , SWCLK,	
1/117	<u> </u>	1/0	3 7 1	SPI1_MOSI ⁽⁵⁾	
				Default: PA15	
PA15	25	I/O	5VT	Alternate: SPI0_NSS, I2S0_WS, USART0_RX ⁽³⁾ ,	
		l	<u> </u>	Alternate. SPIO_NSS, IZSO_WS, USARTO_RX ^(*) ,	



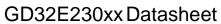
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				USART1_RX ⁽⁴⁾ , SPI1_NSS ⁽⁵⁾ , EVENTOUT
PB3	26	I/O	5VT	Default: PB3
F B3	20	1/0	371	Alternate: SPI0_SCK, I2S0_CK, EVENTOUT
				Default: PB4
PB4	27	I/O	5VT	Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,
				EVENTOUT, I2C0_TXFRAME, TIMER16_BRKIN
	DD5 00 1/0		5VT	Default: PB5
DDC		1/0		Alternate: SPI0_MOSI,I2S0_SD, I2C0_SMBA,
PB5	28	I/O		TIMER15_BRKIN, TIMER2_CH1
				Additional: WKUP5
DDG	00	1/0	5\ /T	Default: PB6
PB6	29	I/O	5VT	Alternate: I2C0_SCL, USART0_TX, TIMER15_CH0_ON
557	00	1/0	5) /T	Default: PB7
PB7	30	I/O	5VT	Alternate:I2C0_SDA, USART0_RX,TIMER16_CH0_ON
воото	31	I		Default: BOOT0
Vss	32	Р		Default: V _{SS}

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Functions are available on GD32E230K4 devices only.
- (4) Functions are available on GD32E230K8/6 devices.
- (5) Functions are available on GD32E230K8 devices only.

2.6.3 GD32E230Kx QFN32 pin definitions

Table 2-6. GD32E230Kx QFN32 pin definitions

Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V_{DD}	1	Р		Default: V _{DD}
				Default: PF0
PF0-OSCIN	2	I/O	5VT	Alternate: I2C0_SDA
				Additional: OSCIN
PF1-				Default: PF1
	3	I/O	-	Alternate: I2C0_SCL
OSCOUT				Additional: OSCOUT
NRST	4	I/O		Default: NRST
V_{DDA}	5	Р		Default: V _{DDA}
				Default: PA0
DAG MIZLID	0	I/O		Alternate: USART0_CTS ⁽³⁾ , USART1_CTS ⁽⁴⁾ , CMP_OUT,
PA0-WKUP	6			I2C1_SCL ⁽⁵⁾
				Additional: ADC_IN0, CMP_IM6, RTC_TAMP1, WKUP0
				Default: PA1
PA1	7	I/O		Alternate: USART0_RTS ⁽³⁾ , USART1_RTS ⁽⁴⁾ ,
			ļ	I2C1_SDA ⁽⁵⁾ , EVENTOUT, TIMER14_CH0_ON ⁽⁵⁾





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Pin Name	Pins	Pin	I/O	Functions description
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	runctions description
				Additional: ADC_IN1, CMP_IP
				Default: PA2
DAG	0	1/0		Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ ,
PA2	8	I/O		TIMER14_CH0 ⁽⁵⁾
				Additional: ADC_IN2, CMP_IM7
				Default: PA3
PA3	9	I/O		Alternate: USART0_RX ⁽³⁾ , USART1_RX ⁽⁴⁾ ,
1 73	3	1/0		TIMER14_CH1 ⁽⁵⁾
				Additional: ADC_IN3
				Default: PA4
PA4	10	I/O		Alternate: SPI0_NSS, I2S0_WS, USART0_CK ⁽³⁾ ,
	10	.,, 0		USART1_CK ⁽⁴⁾ , TIMER13_CH0, SPI1_NSS ⁽⁵⁾
				Additional: ADC_IN4, CMP_IM4
				Default: PA5
PA5	11	I/O		Alternate: SPI0_SCK, I2S0_CK
				Additional: ADC_IN5, CMP_IM5
				Default: PA6
				Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,
PA6	12	I/O		TIMER0_BRKIN, TIMER15_CH0, EVENTOUT,
				CMP_OUT
				Additional: ADC_IN6
				Default: PA7
54-	40			Alternate: SPI0_MOSI, I2S0_SD, TIMER2_CH1,
PA7	13	I/O		TIMER13_CH0, TIMER0_CH0_ON, TIMER16_CH0,
				EVENTOUT
				Additional: ADC_IN7
				Default: PB0
PB0	14	I/O		Alternate: TIMER2_CH2, TIMER0_CH1_ON, USART1_RX ⁽⁴⁾ , EVENTOUT
				Additional: ADC_IN8 Default: PB1
				Alternate: TIMER2_CH3, TIMER13_CH0,
PB1	15	I/O		TIMERO CH2 ON, SPI1 SCK ⁽⁵⁾
				Additional: ADC_IN9
				Default: PB2
PB2	16	I/O	5VT	Alternate: TIMER2_ETI
V _{DD}	17	Р		Default: V _{DD}
VOU	17	Г		Default: PA8
PA8	18	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT,
FA0	10	1/0	371	USART1_TX ⁽⁴⁾ , EVENTOUT
				Default: PA9
PA9	19	I/O	5VT	Alternate: USARTO TX, TIMERO CH1,
17.0		"	J V I	TIMER14_BRKIN ⁽⁵⁾ , I2C0_SCL, CK_OUT
				Default: PA10
PA10	20	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2,
FAIU	20	1/0	371	TIMER16_BRKIN, I2C0_SDA
				THATELY IO_DIVININ, 1200_ODA



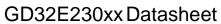
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description		
		- 710		Default: PA11		
PA11	21	I/O	5VT	Alternate: USARTO CTS, TIMERO CH3, CMP OUT,		
				EVENTOUT, SPI1_IO2 ⁽⁵⁾ , I2C0_SMBA, I2C1_SCL ⁽⁵⁾		
				Default: PA12		
PA12	22	I/O	5VT	Alternate: USART0_RTS, TIMER0_ETI, EVENTOUT,		
				SPI1_IO3 ⁽⁵⁾ , I2C0_TXFRAME, I2C1_SDA ⁽⁵⁾		
				Default: PA13		
PA13	23	I/O	5VT	Alternate: SWDIO, IFRP_OUT, SPI1_MISO(5)		
				Default: PA14		
PA14	24	I/O	5VT	Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , SWCLK,		
				SPI1_MOSI ⁽⁵⁾		
				Default: PA15		
PA15	PA15 25 I	I/O	5VT	Alternate: SPI0_NSS, I2S0_WS, USART0_RX ⁽³⁾ ,		
				USART1_RX ⁽⁴⁾ , SPI1_NSS ⁽⁵⁾ , EVENTOUT		
PB3	26	I/O	5VT	Default: PB3		
	20	1/0	371	Alternate: SPI0_SCK, I2S0_CK, EVENTOUT		
				Default: PB4		
PB4	27	I/O	5VT	Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,		
				EVENTOUT, I2C0_TXFRAME, TIMER16_BRKIN		
				Default: PB5		
PB5	28	I/O	5VT	Alternate: SPI0_MOSI,I2S0_SD, I2C0_SMBA,		
1 23	20	1/0	371	TIMER15_BRKIN, TIMER2_CH1		
				Additional: WKUP5		
PB6	29	I/O	5VT	Default: PB6		
. 20		.,,	011	Alternate: I2C0_SCL, USART0_TX, TIMER15_CH0_ON		
PB7	30	I/O	5VT	Default: PB7		
				Alternate:I2C0_SDA, USART0_RX,TIMER16_CH0_ON		
BOOT0	31	I		Default: BOOT0		
PB8	32	I/O	5VT	Default: PB8		
F D0	32	1/0	JV I	Alternate: I2C0_SCL, TIMER15_CH0		

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Functions are available on GD32E230K4 devices only.
- (4) Functions are available on GD32E230K8/6 devices.
- (5) Functions are available on GD32E230K8 devices only.

2.6.4 GD32E230Gx QFN28 pin definitions

Table 2-7. GD32E230Gx QFN28 pin definitions

			•	
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
воото	1	1		Default: BOOT0
PF0-OSCIN	2	I/O	5VT	Default: PF0





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Pin Name	Pins	Pin	1/0	Functions description
		Type ⁽¹⁾	Level ⁽²⁾	·
				Alternate: I2C0_SDA
				Additional: OSCIN
PF1-				Default: PF1
OSCOUT	3	I/O	5VT	Alternate: I2C0_SCL
				Additional: OSCOUT
NRST	4	I/O		Default: NRST
V_{DDA}	5	Р		Default: V _{DDA}
				Default: PA0
PA0-WKUP	6	I/O		Alternate: USART0_CTS ⁽³⁾ , USART1_CTS ⁽⁴⁾ , CMP_OUT,
1 AO-WKOI	O	1/0		I2C1_SCL ⁽⁵⁾
				Additional: ADC_IN0, CMP_IM6, RTC_TAMP1, WKUP0
				Default: PA1
PA1	7	I/O		Alternate: USART0_RTS ⁽³⁾ , USART1_RTS ⁽⁴⁾ ,
IAI	,	1/0		I2C1_SDA ⁽⁵⁾ , EVENTOUT, TIMER14_CH0_ON ⁽⁵⁾
				Additional: ADC_IN1, CMP_IP
				Default: PA2
PA2	8	I/O		Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ ,
FAZ	0	1/0		TIMER14_CH0 ⁽⁵⁾
				Additional: ADC_IN2, CMP_IM7
				Default: PA3
PA3	9	I/O		Alternate: USART0_RX ⁽³⁾ , USART1_RX ⁽⁴⁾ ,
PAS	9	1/0		TIMER14_CH1 ⁽⁵⁾
				Additional: ADC_IN3
				Default: PA4
PA4	10	I/O		Alternate: SPI0_NSS, I2S0_WS, USART0_CK ⁽³⁾ ,
PA4	10	1/0		USART1_CK ⁽⁴⁾ , TIMER13_CH0, SPI1_NSS ⁽⁵⁾
				Additional: ADC_IN4, CMP_IM4
				Default: PA5
PA5	11	I/O		Alternate: SPI0_SCK, I2S0_CK
				Additional: ADC_IN5, CMP_IM5
				Default: PA6
				Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,
PA6	12	I/O		TIMER0_BRKIN, TIMER15_CH0, EVENTOUT,
				CMP_OUT
				Additional: ADC_IN6
				Default: PA7
				Alternate: SPI0_MOSI, I2S0_SD, TIMER2_CH1,
PA7	13	I/O		TIMER13_CH0, TIMER0_CH0_ON, TIMER16_CH0,
				EVENTOUT
				Additional: ADC_IN7
				Default: PB0
PB0	14	I/O		Alternate: TIMER2_CH2, TIMER0_CH1_ON,
FDU	14	1/0		USART1_RX ⁽⁴⁾ , EVENTOUT
				Additional: ADC_IN8
PB1	15	I/O		Default: PB1
ГВІ	10	1/0		Alternate: TIMER2_CH3, TIMER13_CH0,





Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				TIMER0_CH2_ON, SPI1_SCK(5)
				Additional: ADC_IN9
Vss	16	Р		Default: Vss
V_{DD}	17	Р		Default: V _{DD}
				Default: PA8
PA8	18	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT,
				USART1_TX ⁽⁴⁾ , EVENTOUT
				Default: PA9
PA9 ⁽⁶⁾	19	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1,
				TIMER14_BRKIN ⁽⁵⁾ , I2C0_SCL, CK_OUT
				Default: PA10
PA10 ⁽⁶⁾	20	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2,
				TIMER16_BRKIN, I2C0_SDA
DA40	04	1/0	E) /T	Default: PA13
PA13	21	I/O	5VT	Alternate: SWDIO, IFRP_OUT, SPI1_MISO(5)
				Default: PA14
PA14	22	I/O	5VT	Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , SWCLK,
				SPI1_MOSI ⁽⁵⁾
				Default: PA15
PA15	23	I/O	5VT	Alternate: SPI0_NSS, I2S0_WS, USART0_RX ⁽³⁾ ,
				USART1_RX ⁽⁴⁾ , SPI1_NSS ⁽⁵⁾ , EVENTOUT
PB3	24	I/O	5VT	Default: PB3
1 50	2-7	1,0	371	Alternate: SPI0_SCK, I2S0_CK, EVENTOUT
				Default: PB4
PB4	25	I/O	5VT	Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,
				EVENTOUT, I2C0_TXFRAME, TIMER16_BRKIN
				Default: PB5
PB5	26	I/O	5VT	Alternate: SPI0_MOSI,I2S0_SD, I2C0_SMBA,
1 55	20	1/0	3 7 1	TIMER15_BRKIN, TIMER2_CH1
				Additional: WKUP5
PB6	27	I/O	5VT	Default: PB6
1 50	<u> </u>	","	0 1	Alternate: I2C0_SCL, USART0_TX, TIMER15_CH0_ON
PB7	28	I/O	5VT	Default: PB7
FDI	20	1/0	JVI	Alternate:I2C0_SDA,USART0_RX,TIMER16_CH0_ON

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Functions are available on GD32E230G4 devices only.
- (4) Functions are available on GD32E230G8/6 devices.
- (5) Functions are available on GD32E230G8 devices only.
- (6) Pin pair PA11/PA12 can be remapped instead of pin pair PA9/PA10 using SYSCFG_CFG0 register. <u>Table 2-10. Port A alternate functions summary</u> shows PA11/PA12 remap.



2.6.5 GD32E230Fx TSSOP20 pin definitions

Table 2-8. GD32E230Fx TSSOP20 pin definitions

Pin Name	Pins	Pin	1/0	Functions description
		Type ⁽¹⁾	Level ⁽²⁾	D (4 DE0
DEO OCCINI	0	1/0	5VT	Default: PF0
PF0-OSCIN	2	I/O	571	Alternate: I2C0_SDA Additional: OSCIN
				Default: PF1
PF1-	3	I/O	5VT	Alternate: I2C0 SCL
OSCOUT	3	1/0	371	Additional: OSCOUT
NRST	4	I/O		Default: NRST
V _{DDA}	5	P		Default: V _{DDA}
V DDA	3	'		Default: PA0
				Alternate: USART0_CTS ⁽³⁾ , USART1_CTS ⁽⁴⁾ , CMP_OUT,
PA0-WKUP	6	I/O		I2C1_SCL ⁽⁵⁾
				Additional: ADC_IN0, CMP_IM6, RTC_TAMP1, WKUP0
				Default: PA1
				Alternate: USART0_RTS ⁽³⁾ , USART1_RTS ⁽⁴⁾ ,
PA1	7	I/O		I2C1_SDA ⁽⁵⁾ , EVENTOUT
				Additional: ADC_IN1, CMP_IP
				Default: PA2
PA2	8	I/O		Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾
				Additional: ADC_IN2, CMP_IM7
				Default: PA3
PA3	9	I/O		Alternate: USART0_RX ⁽³⁾ , USART1_RX ⁽⁴⁾
				Additional: ADC_IN3
				Default: PA4
DA4	10	1/0		Alternate: SPI0_NSS, I2S0_WS, USART0_CK(3),
PA4	10	I/O		USART1_CK ⁽⁴⁾ , TIMER13_CH0, SPI1_NSS ⁽⁵⁾
				Additional: ADC_IN4, CMP_IM4
				Default: PA5
PA5	11	I/O		Alternate: SPI0_SCK, I2S0_CK
				Additional: ADC_IN5, CMP_IM5
				Default: PA6
				Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,
PA6	12	I/O		TIMER0_BRKIN, TIMER15_CH0, EVENTOUT,
				CMP_OUT
				Additional: ADC_IN6
				Default: PA7
5	40			Alternate: SPI0_MOSI, I2S0_SD, TIMER2_CH1,
PA7	13	I/O		TIMER13_CH0, TIMER0_CH0_ON, TIMER16_CH0,
				EVENTOUT
				Additional: ADC_IN7
DD4	1.4	1/0		Default: PB1
PB1	14	I/O		Alternate: TIMER2_CH3, TIMER13_CH0, TIMER0_CH2_ON, SPI1_SCK ⁽⁵⁾
				TIIVIERU_CHZ_ON, SPIT_SCK(*)



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Additional: ADC_IN9
Vss	15	Р		Default: Vss
V_{DD}	16	Р		Default: V _{DD}
				Default: PA9
PA9 ⁽⁶⁾	17	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1, I2C0_SCL,
				CK_OUT
	PA10 ⁽⁶⁾ 18 I/O 5VT			Default: PA10
PA10 ⁽⁶⁾			I/O 5VT Alternate: USART0_RX, TIMER0_CH2,	
				TIMER16_BRKIN, I2C0_SDA
DA40	40	1/0	E) /T	Default: PA13
PA13	PA13 19 1/O 5VT		501	Alternate: SWDIO, IFRP_OUT, SPI1_MISO(5)
				Default: PA14
PA14	20	I/O	5VT	Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , SWCLK,
				SPI1_MOSI ⁽⁵⁾
BOOT0	1	I		Default: BOOT0

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Functions are available on GD32E230F4 devices only.
- (4) Functions are available on GD32E230F8/6 devices.
- (5) Functions are available on GD32E230F8 devices only.
- (6) Pin pair PA11/PA12 can be remapped instead of pin pair PA9/PA10 using SYSCFG_CFG0 register. *Table 2-10. Port A alternate functions summary* shows PA11/PA12 remap.

2.6.6 GD32E230Fx QFN20 pin definitions

Table 2-9. GD32E230Fx QFN20 pin definitions

Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Default: PF0
PF0-OSCIN	19	I/O	5VT	Alternate: I2C0_SDA
				Additional: OSCIN
PF1-				Default: PF1
	20	I/O	5VT	Alternate: I2C0_SCL
OSCOUT				Additional: OSCOUT
NRST	1	I/O		Default: NRST
V_{DDA}	2	Р		Default: V _{DDA}
				Default: PA0
DAG WIZUD	2	I/O		Alternate: USART0_CTS ⁽³⁾ , USART1_CTS ⁽⁴⁾ , CMP_OUT,
PA0-WKUP	3			I2C1_SCL ⁽⁵⁾
				Additional: ADC_IN0, CMP_IM6, RTC_TAMP1, WKUP0
PA1	4	I/O		Default: PA1



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Pin Name	Pins	Pin	I/O	Functions description
· ····································	1 1110	Type ⁽¹⁾	Level ⁽²⁾	anousile assertation
				Alternate: USART0_RTS ⁽³⁾ , USART1_RTS ⁽⁴⁾ ,
				I2C1_SDA ⁽⁵⁾ , EVENTOUT
				Additional: ADC_IN1, CMP_IP
				Default: PA2
PA2	5	I/O		Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾
				Additional: ADC_IN2, CMP_IM7
				Default: PA3
PA3	6	I/O		Alternate: USART0_RX ⁽³⁾ , USART1_RX ⁽⁴⁾
				Additional: ADC_IN3
				Default: PA4
PA4	7	I/O		Alternate: SPI0_NSS, I2S0_WS, USART0_CK ⁽³⁾ ,
	•	., 0		USART1_CK ⁽⁴⁾ , TIMER13_CH0, SPI1_NSS ⁽⁵⁾
				Additional: ADC_IN4, CMP_IM4
				Default: PA5
PA5	8	I/O		Alternate: SPI0_SCK, I2S0_CK
				Additional: ADC_IN5, CMP_IM5
				Default: PA6
				Alternate: SPI0_MISO, I2S0_MCK, TIMER2_CH0,
PA6	9	I/O		TIMER0_BRKIN, TIMER15_CH0, EVENTOUT,
				CMP_OUT
				Additional: ADC_IN6
				Default: PA7
				Alternate: SPI0_MOSI, I2S0_SD, TIMER2_CH1,
PA7	10	I/O		TIMER13_CH0, TIMER0_CH0_ON, TIMER16_CH0,
				EVENTOUT
				Additional: ADC_IN7
				Default: PB1
PB1	11	I/O		Alternate: TIMER2_CH3, TIMER13_CH0,
				TIMER0_CH2_ON, SPI1_SCK ⁽⁵⁾
		_		Additional: ADC_IN9
Vss	12	Р		Default: Vss
V _{DD}	13	Р		Default: V _{DD}
				Default: PA9
PA9 ⁽⁶⁾	14	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1, I2C0_SCL,
				CK_OUT
				Default: PA10
PA10 ⁽⁶⁾	15	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2,
				TIMER16_BRKIN, I2C0_SDA
PA13	16	I/O	5VT	Default: PA13
1 7/10		",0	J V I	Alternate: SWDIO, IFRP_OUT, SPI1_MISO ⁽⁵⁾
				Default: PA14
PA14	17	I/O	5VT	Alternate: USART0_TX ⁽³⁾ , USART1_TX ⁽⁴⁾ , SWCLK,
				SPI1_MOSI ⁽⁵⁾
BOOT0	18	Ţ		Default: BOOT0

Notes:



- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Functions are available on GD32E230F4 devices only.
- (4) Functions are available on GD32E230F8/6 devices.
- (5) Functions are available on GD32E230F8 devices only.
- (6) Pin pair PA11/PA12 can be remapped instead of pin pair PA9/PA10 using SYSCFG_CFG0 register. *Table 2-10. Port A alternate functions summary* shows PA11/PA12 remap.



2.6.7 GD32E230xx pin alternate functions

Table 2-10. Port A alternate functions summary

Pin	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Name	, v	7	/ · · · <u>-</u>	7 0	7.11	7 0	7 0	77
		USART0_CTS ⁽¹⁾			I2C1_SCL ⁽			CMP_
PA0		/USART1_CTS ⁽²⁾			3)			OUT
)						
		USART0_RTS ⁽¹⁾			I2C1_SDA ⁽	TIMER14		
PA1	EVENTOUT	/USART1_RTS ⁽²⁾			3)	_CH0_O		
)			,	N ⁽³⁾		
PA2	TIMER14_C	USART0_TX ⁽¹⁾ /						
PAZ	H0 ⁽³⁾	USART1_TX ⁽²⁾						
DAG	TIMER14_C	USART0_RX(1)/						
PA3	H1 ⁽³⁾	USART1_RX ⁽²⁾						
D 4 4	SPI0_NSS/I	USART0_CK(1)/			TIMER13_		SPI1_N	
PA4	2S0_WS	USART1_CK ⁽²⁾			CH0		SS ⁽³⁾	
545	SPI0_SCK/I							
PA5	2S0_CK							
	SPI0_MISO/	TIMER2_CH0	TIMER0_BR			TIMER15	EVENT	CMP_
PA6	I2S0_MCK		KIN			_CH0	OUT	OUT
	SPI0_MOSI/	TIMER2_CH1	TIMER0_CH		TIMER13_	TIMER16	EVENT	
PA7	12S0_SD		0_ON		CH0	_CH0	OUT	
	CK_OUT	USART0_CK	TIMER0_CH	EVENT	USART1_T			
PA8			0	OUT	X ⁽²⁾			
	TIMER14_B		TIMER0_CH					
PA9	RKIN ⁽³⁾	USART0_TX	1		I2C0_SCL			
	TIMER16_B		TIMER0_CH					
PA10	RKIN	USART0_RX	2		I2C0_SDA			
			TIMER0_CH		I2C0_SMB	I2C1_SC	SPI1_I	CMP_
PA11	EVENTOUT	USART0_CTS	3		A	L ⁽³⁾	O2 ⁽³⁾	OUT
					I2C0_TXF	I2C1_SD	SPI1_I	
PA12	EVENTOUT	USART0_RTS	TIMER0_ETI		RAME	A ⁽³⁾	O3 ⁽³⁾	
							SPI1_M	
PA13	SWDIO	IFRP_OUT					ISO ⁽³⁾	
		USART0_TX ⁽¹⁾ /					SPI1_M	
PA14	SWCLK	USART1_TX ⁽²⁾					OSI ⁽³⁾	
	SPI0_NSS/I	USARTO_RX ⁽¹⁾ /		EVENT			SPI1_N	
PA15	2S0_WS	USART1_RX ⁽²⁾		OUT			SS ⁽³⁾	
		1 00/						



Table 2-11. Port B alternate functions summary

Table 2-11. Port B alternate functions summary									
Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	
PB0	EVENTOUT	TIMER2_CH2	TIMER0_CH 1_ON		USART1 _RX ⁽²⁾				
PB1	TIMER13_CH 0	TIMER2_CH3	TIMER0 CH				SPI1_S CK ⁽³⁾		
PB2			TIMER2_ET I						
PB3	SPI0_SCK/I2 S0_CK	EVENTOUT							
PB4	SPI0_MISO /I2S0_MCK	TIMER2_CH0	EVENTOUT		I2C0_TX FRAME		TIMER1 6_BRKI N		
PB5	SPI0_MOSI /I2S0_SD	TIMER2_CH1	TIMER15_B RKIN	I2C0_SMBA					
PB6	USART0_TX	I2C0_SCL	TIMER15_C H0_ON						
PB7	USART0_RX	I2C0_SDA	TIMER16_C H0_ON						
PB8		I2C0_SCL	TIMER15_C H0						
PB9	IFRP_OUT	I2C0_SDA	TIMER16_C H0	EVENTOUT		I2S0_M CK		SPI1_N SS ⁽³⁾	
PB10		I2C0_SCL ⁽¹⁾ /I 2C1_SCL ⁽³⁾					SPI1_I O2 ⁽³⁾	SPI1_S CK ⁽³⁾	
PB11	EVENTOUT	I2C0_SDA ⁽¹⁾ /I 2C1_SDA ⁽³⁾					SPI1_I O3 ⁽³⁾		
PB12	SPI0_NSS ⁽¹⁾ /SPI1_NSS ⁽³⁾	EVENTOUT	TIMER0_BR KIN		I2C1_SM BA ⁽³⁾				
PB13	SPI0_SCK ⁽¹⁾ /SPI1_SCK ⁽³⁾	I2C1_TXFRA ME ⁽³⁾	TIMER0_CH 0_ON			I2C1_S CL ⁽³⁾			
PB14	SPI0_MISO ⁽¹⁾ /SPI1_MISO ⁽³⁾	TIMER14_CH 0 ⁽³⁾	TIMER0_CH 1_ON			I2C1_S DA ⁽³⁾			
PB15	SPI0_MOSI ⁽¹⁾ /SPI1_MOSI ⁽³⁾		TIMER0_CH 2_ON	TIMER14_CH 0_ON ⁽³⁾					

Table 2-12. Port F alternate functions summary

Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6
PF0		I2C0_SDA					
PF1		I2C0_SCL					
PF6	I2C0_SCL ⁽¹						



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)/I2C1_SCL			
	(3)			
	I2C0_SDA(
PF7	1)/I2C1_SD			
	A ⁽³⁾			

Notes:

- (1) Functions are available on GD32E230x4 devices only.
- (2) Functions are available on GD32E230x8/6 devices.
- (3) Functions are available on GD32E230x8 devices only.



3 Functional description

3.1 ARM® Cortex®-M23 core

The Cortex-M23 processor is an energy-efficient processor with a very low gate count. It is intended to be used for microcontroller and deeply embedded applications that require an area-optimized processor. The processor is highly configurable enabling a wide range of implementations from those requiring memory protection and powerful trace technology to cost sensitive devices requiring minimal area, while delivering outstanding computational performance and an advanced system response to interrupts.

32-bit ARM® Cortex®-M23 processor core

- Up to 72 MHz operation frequency
- Single-cycle multiplication and hardware divider
- Ultra-low power, energy-efficient operation
- Excellent code density
- Integrated Nested Vectored Interrupt Controller (NVIC)
- 24-bit SysTick timer

The Cortex®-M23 processor is based on the ARMv8-M architecture and supports both Thumb and Thumb-2 instruction sets. Some system peripherals listed below are also provided by Cortex®-M23:

- Internal Bus Matrix connected with AHB master, Serial Wire Debug Port and Single-cycle IO port
- Nested Vectored Interrupt Controller (NVIC)
- Breakpoint Unit(BPU)
- Data Watchpoint and Trace (DWT)
- Serial Wire JTAG Debug Port (SWJ-DP)

3.2 Embedded memory

- Up to 64 Kbytes of Flash memory
- Up to 8 Kbytes of SRAM with hardware parity checking

The ARM® Cortex®-M23 processor is structured in Harvard architecture which can use separate buses to fetch instructions and load/store data. 64 Kbytes of inner Flash and 8 Kbytes of inner SRAM at most is available for storing programs and data, both accessed (R/W) at CPU clock speed with 0~2 wait states. *Table 2-3. GD32E230xx memory map* shows the memory map of the GD32E230xx series of devices, including code, SRAM, peripheral, and other pre-defined regions.



3.3 Clock, reset and supply management

- Internal 8 MHz factory-trimmed RC and external 4 to 32 MHz crystal oscillator
- Internal 28 MHz RC oscillator
- Internal 40 KHz RC calibrated oscillator and external 32.768 KHz crystal oscillator
- Integrated system clock PLL
- 1.8 to 3.6 V application supply and I/Os
- Supply Supervisor: POR (Power On Reset), PDR (Power Down Reset), and low voltage detector (LVD)

The Clock Control Unit (CCU) provides a range of oscillator and clock functions. These include speed internal RC oscillator and external crystal oscillator, high speed and low speed two types. Several prescalers allow the frequency configuration of the AHB and two APB domains. The maximum frequency of the AHB, APB2 and APB1 domains is 72 MHz/72 MHz. See *Figure 2-8. GD32E230xx clock tree* for details on the clock tree.

The Reset Control Unit (RCU) controls three kinds of reset: system reset resets the processor core and peripheral IP components. Power-on reset (POR) and power-down reset (PDR) are always active, and ensures proper operation starting from 2.6 V and down to 1.8V. The device remains in reset mode when V_{DD} is below a specified threshold. The embedded low voltage detector (LVD) monitors the power supply, compares it to the voltage threshold and generates an interrupt as a warning message for leading the MCU into security.

Power supply schemes:

- V_{DD} range: 1.8 to 3.6 V, external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} range: 1.8 to 3.6 V, external analog power supplies for ADC, reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAK} range: 1.8 to 3.6 V, power supply for RTC, external clock 32 KHz oscillator and backup registers (through power switch) when V_{DD} is not present.

3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from main Flash memory (default)
- Boot from system memory
- Boot from on-chip SRAM

In default condition, boot from main Flash memory is selected. The boot loader is located in the internal boot ROM memory (system memory). It is used to reprogram the Flash memory by using USART0 (PA9 and PA10) or USART1 (PA14 and PA15).



3.5 Power saving modes

The MCU supports three kinds of power saving modes to achieve even lower power consumption. They are sleep mode, deep-sleep mode, and standby mode. These operating modes reduce the power consumption and allow the application to achieve the best balance between the CPU operating time, speed and power consumption.

■ Sleep mode

In sleep mode, only the clock of CPU core is off. All peripherals continue to operate and any interrupt/event can wake up the system.

■ Deep-sleep mode

In deep-sleep mode, all clocks in the 1.2V domain are off, and all of the high speed crystal oscillator (IRC8M, HXTAL) and PLL are disabled. Only the contents of SRAM and registers are retained. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep mode including the 16 external lines, the RTC alarm, RTC tamper and timestamp, CMP output, LVD output and USART wakeup. When exiting the deep-sleep mode, the IRC8M is selected as the system clock.

Standby mode

In standby mode, the whole 1.2V domain is power off, the LDO is shut down, and all of IRC8M, HXTAL and PLL are disabled. The contents of SRAM and registers (except backup registers) are lost. There are four wakeup sources for the standby mode, including the external reset from NRST pin, the RTC alarm, the FWDGT reset, and the rising edge on WKUP pin.

3.6 Analog to digital converter (ADC)

- 12-bit SAR ADC's conversion rate is up to 2 MSPS
- 12-bit, 10-bit, 8-bit or 6-bit configurable resolution
- Hardware oversampling ratio adjustable from 2 to 256x improves resolution to 16-bit
- Input voltage range: V_{SSA} to V_{DDA}
- Temperature sensor

One 12-bit 2 MSPS multi-channel ADC is integrated in the device. It has a total of 12 multiplexed channels: up to 10 external channels, 1 channel for internal temperature sensor (V_{SENSE}) and 1 channel for internal reference voltage (V_{REFINT}). The input voltage range is between V_{SSA} and V_{DDA}. An on-chip hardware oversampling scheme improves performance while off-loading the related computational burden from the CPU. An analog watchdog block can be used to detect the channels, which are required to remain within a specific threshold window. A configurable channel management block can be used to perform conversions in single, continuous, scan or discontinuous mode to support more advanced use.

The ADC can be triggered from the events generated by the general level 0 timers (TIMERx) and the advanced timer (TIMER0) with internal connection. The temperature sensor can be used to generate a voltage that varies linearly with temperature. It is internally connected to



the ADC_IN16 input channel which is used to convert the sensor output voltage in a digital value.

3.7 DMA

- 5 channels DMA controller
- Peripherals supported: Timers, ADC, SPIs, I2Cs, USARTs and I2S

The flexible general-purpose DMA controllers provide a hardware method of transferring data between peripherals and/or memory without intervention from the CPU, thereby freeing up bandwidth for other system functions. Three types of access method are supported: peripheral to memory, memory to peripheral, memory to memory.

Each channel is connected to fixed hardware DMA requests. The priorities of DMA channel requests are determined by software configuration and hardware channel number. Transfer size of source and destination are independent and configurable.

3.8 General-purpose inputs/outputs (GPIOs)

- Up to 39 fast GPIOs, all mappable on 16 external interrupt lines
- Analog input/output configurable
- Alternate function input/output configurable

There are up to 39 general purpose I/O pins (GPIO) in GD32E230xx, named PA0 \sim PA15 and PB0 \sim PB15, PC13 \sim PC15, PF0 \sim PF1, PF6 \sim PF7 to implement logic input/output functions. Each of the GPIO ports has related control and configuration registers to satisfy the requirements of specific applications. The external interrupts on the GPIO pins of the device have related control and configuration registers in the Interrupt/event controller (EXTI). The GPIO ports are pin-shared with other alternative functions (AFs) to obtain maximum flexibility on the package pins. Each of the GPIO pins can be configured by software as output (push-pull open-drain or analog), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current capable except for analog inputs.

3.9 Timers and PWM generation

- One 16-bit advanced timer (TIMER0), up to five 16-bit general timers (TIMER2, TIMER13
 ~ TIMER16), and one 16-bit basic timer (TIMER5)
- Up to 4 independent channels of PWM, output compare or input capture for each general timer and external trigger input
- 16-bit, motor control PWM advanced timer with programmable dead-time generation for output match
- Encoder interface controller with two inputs using quadrature decoder



- 24-bit SysTick timer down counter
- 2 watchdog timers (free watchdog timer and window watchdog timer)

The advanced timer (TIMER0) can be used as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable dead-time generation. It can also be used as a complete general timer. The 4 independent channels can be used for input capture, output compare, PWM generation (edge- or center- aligned counting modes) and single pulse mode output. If configured as a general 16-bit timer, it has the same functions as the TIMERx timer. It can be synchronized with external signals or to interconnect with other general timers together which have the same architecture and features.

The general timer can be used for a variety of purposes including general time, input signal pulse width measurement or output waveform generation such as a single pulse generation or PWM output, up to 4 independent channels for input capture/output compare. TIMER2 is based on a 16-bit auto-reload up/down counter and a 16-bit prescaler. TIMER13 ~ TIMER16 is based on a 16-bit auto-reload up counter and a 16-bit prescaler. The general timer also supports an encoder interface with two inputs using quadrature decoder.

The basic timer, known as TIMER5 can also be used as a simple 16-bit time base.

The GD32E230xx have two watchdog peripherals, free watchdog and window watchdog. They offer a combination of high safety level, flexibility of use and timing accuracy.

The free watchdog timer includes a 12-bit down-counting counter and an 8-bit prescaler. It is clocked from an independent 40 KHz internal RC and as it operates independently of the main clock, it can operate in deep-sleep and standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management.

The window watchdog is based on a 7-bit down counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early wakeup interrupt capability and the counter can be frozen in debug mode.

The SysTick timer is dedicated for OS, but could also be used as a standard down counter. The features are shown below:

- A 24-bit down counter
- Auto reload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

3.10 Real time clock (RTC)

- Independent binary-coded decimal (BCD) format timer/counter with five 32-bit backup registers.
- Calendar with subsecond, second, minute, hour, week day, date, year and month automatically correction



- Alarm function with wake up from deep-sleep and standby mode capability
- On-the-fly correction for synchronization with master clock. Digital calibration with 0.954 ppm resolution for compensation of quartz crystal inaccuracy.

The real time clock is an independent timer which provides a set of continuously running counters in backup registers to provide a real calendar function, and provides an alarm interrupt or an expected interrupt. It is not reset by a system or power reset, or when the device wakes up from standby mode. In the RTC unit, there are two prescalers used for implementing the calendar and other functions. One prescaler is a 7-bit asynchronous prescaler and the other is a 15-bit synchronous prescaler.

3.11 Inter-integrated circuit (I2C)

- Up to two I2C bus interfaces can support both master and slave mode with a frequency up to 1 MHz (Fast mode plus)
- Provide arbitration function, optional PEC (packet error checking) generation and checking
- Supports 7-bit and 10-bit addressing mode and general call addressing mode
- Supports SAM_V mode

The I2C interface is an internal circuit allowing communication with an external I2C interface which is an industry standard two line serial interface used for connection to external hardware. These two serial lines are known as a serial data line (SDA) and a serial clock line (SCL). The I2C module provides different data transfer rates: up to 100 KHz in standard mode, up to 400 KHz in the fast mode and up to 1 MHz in the fast mode plus. The I2C module also has an arbitration detect function to prevent the situation where more than one master attempts to transmit data to the I2C bus at the same time. A CRC-8 calculator is also provided in I2C interface to perform packet error checking for I2C data.

3.12 Serial peripheral interface (SPI)

- Up to two SPI interfaces with a frequency of up to 18 MHz
- Support both master and slave mode
- Hardware CRC calculation and transmit automatic CRC error checking
- Separate transmit and receive 32-bit FIFO with DMA capability (only in SPI1)
- Data frame size can be 4 to 16 bits (only in SPI1)
- Quad-SPI configuration available in master mode (only in SPI1)

The SPI interface uses 4 pins, among which are the serial data input and output lines (MISO & MOSI), the clock line (SCK) and the slave select line (NSS). Both SPIs can be served by the DMA controller. The SPI interface may be used for a variety of purposes, including simplex synchronous transfers on two lines with a possible bidirectional data line or reliable communication using CRC checking. Specially, SPI1 has separate transmit and receive 32-bit FIFO with DMA capability and its data frame size can be 4 to 16 bits. Quad-SPI master



mode is also supported in SPI1.

3.13 Universal synchronous asynchronous receiver transmitter (USART)

- Up to two USARTs with operating frequency up to 4.5 MBits/s
- Supports both asynchronous and clocked synchronous serial communication modes
- IrDA SIR encoder and decoder support
- LIN break generation and detection
- ISO 7816-3 compliant smart card interface

The USART (USART0, USART1) are used to translate data between parallel and serial interfaces, provides a flexible full duplex data exchange using synchronous or asynchronous transfer. It is also commonly used for RS-232 standard communication. The USART includes a programmable baud rate generator which is capable of dividing the system clock to produce a dedicated clock for the USART transmitter and receiver. The USART also supports DMA function for high speed data communication.

3.14 Inter-IC sound (I2S)

- One I2S bus Interfaces with sampling frequency from 8 KHz to 192 KHz, multiplexed with SPI0
- Support either master or slave mode

The Inter-IC sound (I2S) bus provides a standard communication interface for digital audio applications by 3-wire serial lines. GD32E230xx contain an I2S-bus interface that can be operated with 16/32 bit resolution in master or slave mode, pin multiplexed with SPI0. The audio sampling frequency from 8 KHz to 192 KHz is supported with less than 0.5% accuracy error.

3.15 Comparators (CMP)

- One fast rail-to-rail low-power comparators with software configurable
- Programmable reference voltage (internal or external I/O)

One Comparator (CMP) is implemented within the devices. It can wake up from deep-sleep mode to generate interrupts and breaks for the timers and also can be combined as a window comparator. The internal voltage reference is also connected to ADC_IN17 input channel of the ADC.



3.16 Debug mode

■ Serial wire JTAG debug port (SWJ-DP)

The ARM® SWJ-DP Interface is embedded and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

3.17 Package and operation temperature

- LQFP48 (GD32E230CxTx), LQFP32 (GD32E230KxTx), QFN32 (GD32E230KxUx), QFN28 (GD32E230GxUx), TSSOP20 (GD32E230FxPx) and QFN20 (GD32E230FxUx).
- Operation temperature range: -40°C to +85°C (industrial level)



4 Electrical characteristics

4.1 Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 4-1. Absolute maximum ratings

Symbol	Parameter	Min	Max	Unit
V_{DD}	External voltage range ⁽¹⁾	V _{SS} - 0.3	V _{SS} + 3.6	V
V_{DDA}	External analog supply voltage	V _{SSA} - 0.3	V _{SSA} + 3.6	V
Vin	Input voltage on 5V tolerant pin(2)	V _{SS} - 0.3	$V_{DD} + 4.0$	V
VIN	Input voltage on other I/O	V _{SS} - 0.3	4.0	V
$ \Delta V_{DDx} $	Variations between different V _{DD} power pins	_	50	mV
Vssx -Vss	Variations between different ground pins	_	50	mV
lio	Maximum current for GPIO pins	_	25	mA
1	Injected current on 5V tolerant pin	_	-5/+0	mA
I _{INJ}	Injected current on other I/O	_	±5	mA
∑l _{INJ}	Injected current on all I/O(3)	_	±25	mA
TA	Operating temperature range	-40	+85	°C
T _{STG}	Storage temperature range	-55	+150	°C
TJ	Maximum junction temperature	_	125	°C

⁽¹⁾ All main power and ground pins should be connected to an external power source within the allowable range.

4.2 Operating conditions characteristics

Table 4-2. DC operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	Supply voltage	_	1.8	3.3	3.6	V
V _{DDA}	Analog supply voltage ADC not used		1.8	3.3	3.6	V
	Analog supply voltage ADC used	_	2.4	3.3	3.6	V

⁽²⁾ V_{IN} maximum value cannot exceed 6.9V and it must be below the maximum allowable injection current value refer to <u>Table 4-1. Absolute maximum ratings</u>.

⁽³⁾ The maximum Σ IINJ(PIN) is the absolute sum of the negative and positive injection currents (instantaneous values).



Table 4-3. Clock frequency

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	AHB clock frequency	_	0	72	MHz
f _{APB1}	APB1 clock frequency	_	0	72	MHz
f _{APB2}	APB2 clock frequency	_	0	72	MHz

Table 4-4. Operating conditions at Power up/ Power down

Symbol	Parameter	Conditions	Min	Max	Unit
4 (1)	V _{DD} rise time rate		20	8	us/V
t _{VDD} ⁽¹⁾	V _{DD} fall time rate	_	20	8	u5/ v

Table 4-5. Start-up timings of Operating conditions

Symbol	Parameter	Conditions	Тур	Unit
t _{start-up} ⁽¹⁾	Start-up time	Clock source from HXTAL	432	
		Clock source from IRC8M	76	μs

^{(1).} After power-up, the start-up time is the time between the rising edge of NRST high and the main function.

Table 4-6. Power saving mode wakeup timings characteristics

Symbol	Parameter	Тур	Unit
t _{Sleep} (1)	Wakeup from Sleep mode	3.5	
t- · (1)	Wakeup from Deep-sleep mode (LDO On)	17.1	
t _{Deep-sleep} (1)	Wakeup from Deep-sleep mode (LDO in low power mode)	17.1	μs
t _{Standby} (1)	Wakeup from Standby mode	77.5	

^{(1).} The wakeup times is measured from the wakeup event to the point at which the application code reads the first instruction under the the below conditions:

4.3 Power consumption

The power measurements specified in the tables represent that code with data executing from embedded Flash with the following specifications.

Table 4-7. Power consumption characteristics

Symbol	Parameter	eter Conditions I		Тур	Max	Unit
		V_{DD} = V_{DDA} =3.3 V , HXTAL=8 MHz , System	_	8.5	_	mA
		clock=72 MHz, All peripherals enabled				
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System	_	5.4	_	mA
	Supply current (Run mode)	clock =72 MHz, All peripherals disabled				,
I _{DD}		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		6.2		mA
.55		clock=48 MHz, All peripherals enabled		0.2		
		V_{DD} = V_{DDA} =3.3 V , HXTAL=8 M Hz, System	_	4.2		mA
		clock =48 MHz, All peripherals disabled		1.2		1117 (
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System	_	5.1	_	mA
		clock=36 MHz, All peripherals enabled				,

 V_{DD} = V_{DDA} =3.3V, IRC8M=System clock=8MHz



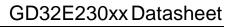
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Symbol	Parameter	Conditions Min 1		Тур	Max	Unit
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		- 76	111022	
		clock =36 MHz, All peripherals disabled		3.6		mΑ
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System				
		clock=24 MHz, All peripherals enabled	_	4.0		mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System				_
		clock =24 MHz, All peripherals disabled	_	2.9	_	mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System				_
		clock=16 MHz, All peripherals enabled		3.2		mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		0.5		
		clock =16 MHz, All peripherals disabled	_	2.5	_	mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System				
		clock=8 MHz, All peripherals enabled	_	2.4	_	mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		0.4		
		clock =8 MHz, All peripherals disabled		2.1		mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		0.0		^
		clock=4 MHz, All peripherals enabled	_	0.8		mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		0.0		^
		clock =4 MHz, All peripherals disabled	_	0.6	_	mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		0.6		A
		clock=2 MHz, All peripherals enabled		0.6		mA
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, System		0.5		mA
		clock =2 MHz, All peripherals disabled		0.5		шА
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				
		off, System clock =72 MHz, All peripherals	_	7.4	_	mΑ
		enabled				
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				
		off, System clock =72 MHz, All peripherals	_	3.7		mΑ
		disabled				
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				
		off, System clock =48 MHz, All peripherals		5.5		mA
		enabled				
	Supply current	V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				
	(Sleep mode)	off, System clock =48 MHz, All peripherals	_	3.1		mA
	(Gloop mode)	disabled				
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				
		off, System clock =36 MHz, All peripherals	_	4.5	_	mA
		enabled				
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				_
		off, System clock =36 MHz, All peripherals		2.7		mA
		disabled				
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock				_
		off, System clock =24 MHz, All peripherals	-	3.6	_	mA
		enabled				



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Symbol	Parameter	Conditions Min Typ Ma				Max	Unit
Syllibol	Farameter		IVIIII	тур	IVIAX	Ollic	
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock		0.4		A	
		off, System clock =24 MHz, All peripherals	_	2.4	_	mA	
		disabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock					
		off, System clock =16 MHz, All peripherals		3.0		mA	
		enabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock					
		off, System clock =16 MHz, All peripherals	_	2.1	_	mA	
		disabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock					
		off, System clock =8 MHz, All peripherals	_	2.3		mΑ	
		enabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock					
		off, System clock =8 MHz, All peripherals	1.9	1.9		mA	
		disabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock					
		off, System clock =4 MHz, All peripherals	_	0.7	_	mA	
		enabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock					
		off, System clock =4 MHz, All peripherals	_	0.5		mA	
		disabled		0.0		1117	
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock		0.5		m ^	
		off, System clock =2 MHz, All peripherals		0.5		mA	
		enabled					
		V _{DD} =V _{DDA} =3.3V, HXTAL=8MHz, CPU clock		0.4		^	
		off, System clock =2 MHz, All peripherals	_	0.4		mA	
		disabled					
		V _{DD} =V _{DDA} =3.3V, Regulator in run mode,					
	Supply current	IRC40K off, RTC off, All GPIOs analog	_	25.5	_	μΑ	
	(Deep-sleep	mode					
1	mode)	V _{DD} =V _{DDA} =3.3V, Regulator in low power					
	mode)	mode, IRC40K off, RTC off, All GPIOs	_	12.3		μΑ	
		analog mode					
		V _{DD} =V _{DDA} =3.3V, LXTAL off, IRC40K on,		3.8		11.4	
		RTC on	_	3.0		μΑ	
		V _{DD} =V _{DDA} =3.3V, LXTAL off, IRC40K on,		2.6			
	Supply current	RTC off	_	3.6		μΑ	
	(Standby mode)	V _{DD} =V _{DDA} =3.3V, LXTAL off, IRC40K off,		6.1			
		RTC off, VDDA Monitor on	_	3.1	_	μΑ	
		V _{DD} =V _{DDA} =3.3V, LXTAL off, IRC40K off,					
		RTC off, VDDA Monitor off	-	1.6	_	μΑ	
		V _{DD} =V _{DDA} =3.6 V, LXTAL on with external					
LIVEN SES	LXTAL+RTC	crystal, RTC on, Higher driving	_	1.43		μΑ	
I _{LXTAL+RTC}	current			1 26		1	
		V _{DD} =V _{DDA} =3.3 V, LXTAL on with external		1.36		μΑ	





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		crystal, RTC on, Higher driving				
		V _{DD} =V _{DDA} =2.5 V, LXTAL on with external		4.00		
		crystal, RTC on, Higher driving		1.23		μΑ
		V _{DD} =V _{DDA} =1.8 V, LXTAL on with external		1.15		110
		crystal, RTC on, Higher driving		1.13		μΑ
		V _{DD} =V _{DDA} =3.6 V, LXTAL on with external		1.13		μA
		crystal, RTC on, Medium High driving		1.10		μΛ
		V_{DD} = V_{DDA} =3.3 V, LXTAL on with external		1.06		μΑ
		crystal, RTC on, Medium High driving		1.00		μπ
		V_{DD} = V_{DDA} =2.5 V, LXTAL on with external	_	_ 0.95	_	μΑ
		crystal, RTC on, Medium High driving				μ
		V _{DD} =V _{DDA} =1.8 V, LXTAL on with external	_	0.86	_	μΑ
		crystal, RTC on, Medium High driving				'
		V _{DD} =V _{DDA} =3.6 V, LXTAL on with external		0.84	_	μΑ
		crystal, RTC on, Medium Low driving				•
		V _{DD} =V _{DDA} =3.3 V, LXTAL on with external	_	0.76		μΑ
		crystal, RTC on, Medium Low driving				•
		V _{DD} =V _{DDA} =2.5 V, LXTAL on with external	_	0.64		μΑ
		crystal, RTC on, Medium Low driving				-
		V _{DD} =V _{DDA} =1.8 V, LXTAL on with external	_	0.56	_	μΑ
		crystal, RTC on, Medium Low driving				_
		V _{DD} =V _{DDA} =3.6 V, LXTAL on with external	_	0.74	_	μΑ
		crystal, RTC on, Low driving				
		V _{DD} =V _{DDA} =3.3 V, LXTAL on with external	_	0.67	_	μΑ
		crystal, RTC on, Low driving				
		V _{DD} =V _{DDA} =2.5 V, LXTAL on with external	_	0.56		μΑ
		crystal, RTC on, Low driving				
		V _{DD} =V _{DDA} =1.8 V, LXTAL on with external	_	0.47	_	μΑ
		crystal, RTC on, Low driving				

Notes:

- (1) When System Clock is less than 4MHz, an external source is used, and the HXTAL bypass function is needed, no PLL.
- (2) When System Clock is greater than 8MHz, a crystal 8MHz is used, and the HXTAL bypass function is closed, using PLL.
- (3) When analog peripheral blocks such as ADCs, HXTAL, LXTAL, IRC8M, or IRC40K are ON, an additional power consumption should be considered

The power measurements specified in the tables represent that code with data executing from embedded Flash with the following specifications.

Table 4-8. Peripheral current consumption characteristics

Peripherials ⁽¹⁾		Typical consumption at 25℃ (TYP)	Unit
APB1	PMU	1.44	mA



	Peripherials ⁽¹⁾	Typical consumption at 25℃ (TYP)	Unit
	I2C1	1.38	
	I2C0	1.38	
	USART1	1.34	
	SPI1	1.37	
	WWDGT	1.32	
	TIMER13	1.36	
	TIMER5	0.17	
	TIMER2	0.23	
	DBG	1.3	
	TIMER16	1.42	
	TIMER15	1.42	
	TIMER14	1.49	
APB2	USART0	1.63	
	SPI0	1.38	
	TIMER0	1.68	
	ADC ⁽²⁾	0.95	
	SYSCFG & CMP ⁽³⁾	1.27	
	GPIOF	1.31	
	GPIOC	1.31	
ALID	GPIOB	1.34	
AHB	GPIOA	1.34	
	CRC	0.16	
	DMA	0.15	

⁽¹⁾ Conditons: $V_{DD} = V_{DDA} = 3.3V$, IRC8M = 8MHz, system clock = $f_{HCLK} = 72$ MHz, $f_{APB1} = f_{APB2} = f_{HCLK}$.

4.4 EMC characteristics

EMS (electromagnetic susceptibility) includes ESD (Electrostatic discharge, positive and negative) and FTB (Burst of Fast Transient voltage, positive and negative) testing result is given in *Table 4-9. EMS characteristics*, based on the EMS levels and classes compliant with IEC 61000 series standard.

Table 4-9. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
	Voltage applied to all device pins to	$V_{DD} = 3.3 \text{ V}, T_A = +25 ^{\circ}\text{C},$	
V _{ESD}	induce a functional disturbance	LQFP48, f _{HCLK} = 72MHz	ЗА
	induce a functional disturbance	conforms to IEC 61000-4-2	
V _{FTB}	Fast transient voltage burst applied to	$V_{DD} = 3.3 \text{ V}, T_A = +25 \text{ °C},$	4A

⁽²⁾ ADC: f_{ADCCLK} = IRC28M, ADCON bit set to 1 in ADC_CTL1.

⁽³⁾ CMP: CMP enabled by setting CMPEN bit in CMP_CS, CMP mode set to High Speed.



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induce a functional disturbance through	LQFP48, f _{HCLK} = 72MHz	
100 pF on V _{DD} and V _{SS} pins	conforms to IEC 61000-4-4	

EMI (Electromagnetic Interference) emission testing result is given in <u>Table 4-10. EMI</u> <u>characteristics</u>, compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 4-10. EMI characteristics

Symbol	Parameter			Cond	ditions	Unit
			frequency band	48M	72M	
		$V_{DD} = 3.3 \text{ V},$	0.1 to 2 MHz	1	_	
		$T_A = +25 ^{\circ}C$	2 to 30 MHz	_	_	
S _{EMI} Peak leve	Peak level	compliant with IEC	30 to 130 MHz	_	_	dBµV
		61967-2	130 MHz to 1GHz	_	_	



4.5 Power supply supervisor characteristics

Table 4-11. Power supply supervisor characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		LVDT[2:0]=000, rising edge		2.11	_	V
		LVDT[2:0]=000, falling edge	_	2.01	_	V
	LVDT[2:0]=000, rising edge	_	V			
		LVDT[2:0]=001, falling edge	_	2.16	_	V
		LVDT[2:0]=010, rising edge	_	2.39	_	V
		LVDT[2:0]=010, falling edge	_	2.29	_	V
		LVDT[2:0]=011, rising edge	_	2.52	_	V
M	Low Voltage Detector	LVDT[2:0]=011, falling edge	_	2.43	_	V
VLVD	Threshold	LVDT[2:0]=100, rising edge	_	2.66	_	V
		LVDT[2:0]=100, falling edge	_	2.57		V
		LVDT[2:0]=101, rising edge	_	2.80	_	V
	LVDT[2:0]=000, falling edge	V				
		V				
LVDT[2:0]=101, rising edge — 2.80 — LVDT[2:0]=101, falling edge — 2.71 — LVDT[2:0]=110, rising edge — 2.95 — LVDT[2:0]=110, falling edge — 2.84 —	_	V				
		LVDT[2:0]=111, rising edge	_	3.08	_	V
		LVDT[2:0]=111, falling edge	_	2.11 — 2.01 — 2.25 — 2.16 — 2.39 — 2.29 — 2.52 — 2.43 — 2.66 — 2.57 — 2.80 — 2.71 — 2.95 — 2.84 — 3.08 — 2.98 — 100 n 1.67 — 40 —	V	
V _L VDhyst ⁽¹⁾	LVD hysteresis	_		100		mV
V _{POR}		Rising edge	_	1.71	_	V
V _{PDR}		Falling edge	_	1.67	_	V
V _{PDRhyst} ⁽¹⁾	PDR hysteresis	_	_	40	_	mV
t RSTTEMP	Reset temporization	-	_	2.5	_	ms

⁽¹⁾ Based on design, not actual test values.

4.6 Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up



(LU) test is based on the two measurement methods.

Table 4-12. ESD characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
M	Electrostatic discharge	T _A =25 °C; JESD22-			6000	V
VESD(HBM)	voltage (human body model)	A114	_		6000	V
\/	Electrostatic discharge	T _A =25 °C;			2000	V
VESD(CDM)	voltage (charge device model)	JESD22-C101	_	_	2000	V

Table 4-13. Static latch-up characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
LU	I-test	T _A =25 °C; JESD78	_	_	±200	mA
	V _{supply} over voltage	1A=25 C, JESD/6	_	_	5.4	V

4.7 External clock characteristics

Table 4-14. High speed external clock (HXTAL) generated from a crystal/ceramic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HXTAL}	Crystal or ceramic frequency ⁽¹⁾	V _{DD} =3.3V	4	8	32	MHz
R _F	Feedback resistor	V _{DD} =3.3V	_	_	_	_
	Recommended matching					
CHXTAL	capacitance on OSCIN and	_	_	20	30	pF
	OSCOUT					
language.	Crystal or ceramic operating	V _{DD} =3.3V, T _A =25°C		1.0		m۸
I _{DD(HXTAL)}	current	VDD=3.3V, TA=23 C		1.0		mA
G (INCTAL)	Crystal or ceramic	Startup			_	mA/
G m(HXTAL)	transconductance	Startup				V
ts	Crystal or ceramic startup time	V _{DD} =3.3V, T _A =25°C	_	2	_	ms

⁽¹⁾ Based on design, not actual test values.

Note: $C_{HXTAL1} = C_{HXTAL2} = 2*(C_{LOAD} - C_S)$, For C_{HXTAL1} and C_{HXTAL2} , it is recommended matching capacitance on OSCIN and OSCOUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S , it is PCB and MCU pin stray capacitance (Typ. $C_S = 10pf$).

Table 4-15. High speed external user clock characteristics (HXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f HXTAL_ext	External clock source or oscillator frequency	V _{DD} =3.3V	1	8	50	MHz
V _{HXTALH}	OSCIN input pin high level voltage	V 2 2V	0.7V _D	_	V _{DD}	V
V _{HXTALL}	OSCIN input pin low level voltage	V _{DD} =3.3V	V _{SS}	_	0.3V _D	V



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{H/L(HXTAL)} (1)	OSCIN high or low time	_	5	_		20
t _{R/F(HXTAL)} (1)	OSCIN rise or fall time	_	_	_	10	ns
C _{IN} ⁽¹⁾	OSCIN input capacitance	_	_	5		pF
DuCy _(HXTAL)	Duty cycle	_	30	50	70	%

⁽¹⁾ Based on design, not actual test values.

Table 4-16. Low speed external clock (LXTAL) generated from a crystal/ceramic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL} (1)	Crystal or ceramic frequency	V _{DD} =3.3V		32.768		KHz
R _F	Feedback resistor	V _{DD} =3.3V		_		ΜΩ
CLXTAL ⁽¹⁾	Recommended matching capacitance on OSC32IN and OSC32OUT	_		_	15	pF
		V _{DD} =3.3V, High Drive		1.2		
	Crystal or ceramic operating	V _{DD} =3.3V, Medium High Drive		1.0		
IDD(LXTAL)	current	V _{DD} =3.3V, Medium Low Drive	_	0.6	_	μA
		V _{DD} =3.3V, Low Drive		0.5		
G m(LXTAL)	Crystal or ceramic transconductance	Startup		_		μΑ/ V
tsulxtal	Crystal or ceramic startup time	V _{DD} =3.3V		2		S

⁽¹⁾ Based on design, not actual test values.

Note: $C_{LXTAL1} = C_{LXTAL2} = 2*(C_{LOAD} - C_S)$, For C_{LXTAL1} and C_{LXTAL2} , it is recommended matching capacitance on OSC32IN and OSC32OUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S , it is PCB and MCU pin stray capacitance (Typ. $C_S = 2pf \sim 7pf$).

Table 4-17. Low speed external clock (LXTAL) generated from an external clock source/oscillator characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL_ext} (1)	External clock source or	V _{DD} =3.3V		22 769	1000	kHz
'LX IAL_ext` /	oscillator frequency	VD=3.3V		32.700.	1000	KI IZ
V _{LXTALH}	OSC32IN input pin high level		0.7\/		Max 1000 V _{DD} 0.3V _D D 50 70	
VLXTALH	voltage	V _{DD} =3.3V	0.7 000	_	V DD	V
V	OSC32IN input pin low level	VDD=3.3 V	Vee		0.3V _D	V
VLXTALL	voltage		VSS	_	768. 1000 H - V _{DD} - 0.3V _D - D 50 5	
t _{H/L(LXTAL)} (1)	OSC32IN high or low time	_	450	_	_	20
t _{R/F(LXTAL)} (1)	OSC32IN rise or fall time	_	0.7V _{DD} —	50	ns	
C _{IN} ⁽¹⁾	OSC32IN input capacitance			5	_	pF
DuCy _(LXTAL)	Duty cycle		30	50	70	%

⁽¹⁾ Based on design, not actual test values.



4.8 Internal clock characteristics

Table 4-18. High speed internal clock (IRC8M) characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
firc8M	High Speed Internal Oscillator (IRC8M) frequency	V _{DD} =3.3V	_	8	_	MHz
	IDC9M appillator Fraguency	V_{DD} =3.3V, T_A =-40°C ~ +105°C ⁽²⁾	-4.0	8 — 0 — +5.0 0 — +2.0 0 — +1.0	%	
	IRC8M oscillator Frequency accuracy, Factory-trimmed	V_{DD} =3.3V, T_A =0°C ~ +85°C ⁽²⁾	-2.0		+2.0	%
ACCIRC8M	accuracy, r actory-trimmed	V _{DD} =3.3V, T _A =25°C	-1.0	1	+1.0	%
	IRC8M oscillator Frequency accuracy, User trimming step	_	-	0.5	_	%
D _{IRC8M}	IRC8M oscillator duty cycle	V _{DD} =3.3V, f _{IRC8M} =8MHz	45	50	55	%
IDDIRC8M	IRC8M oscillator operating current	V _{DD} =3.3V, f _{IRC8M} =8MHz	_	55	80	μA
t _{SUIRC8M} (3)	IRC8M oscillator startup time	V _{DD} =3.3V, f _{IRC8M} =8MHz	I	1.5	2	us

⁽¹⁾ V_{DD} = 3.3 V, T_A = -40 to 105 °C unless otherwise specified.

Table 4-19. High speed internal clock (IRC28M) characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	High Speed Internal					
f _{IRC28M}	Oscillator (IRC28M)	V _{DD} =3.3V	_	28	_	MHz
	frequency					
	IRC28M oscillator Frequency	V _{DD} =3.3V, T _A =-40°C ~+105°C ⁽²⁾	-4.0		+5.0	%
	accuracy, Factory-trimmed	V _{DD} =3.3V, T _A =0°C ~ +85°C ⁽²⁾	-3.0	_	+3.0	%
ACCIRC28M		V _{DD} =3.3V, T _A =25°C	-2.0	_	+2.0	%
	IRC28M oscillator Frequency accuracy, User trimming step	_	_	0.5	_	%
D _{IRC28M}	IRC28M oscillator duty cycle	V _{DD} =3.3V, f _{IRC28M} =16MHz	45	50	55	%
IDDIRC28M	IRC28M oscillator operating current	V _{DD} =3.3V, f _{IRC28M} =16MHz	_	140	200	μΑ
t _{SUIRC28M} (3)	IRC28M oscillator startup time	V _{DD} =3.3V, f _{IRC28M} =16MHz	_	1.5	2	μs

⁽¹⁾ VDD = 3.3 V, TA = -40 to 105 °C unless otherwise specified.

Table 4-20. Low speed internal clock (IRC40K) characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f =(2)	Low Speed Internal oscillator	V _{DD} =V _{DDA} =3.3V,	30	38.5	60	KHz
firc40K ⁽²⁾	(IRC40K) frequency	T _A =-40°C ~ +85°C	30			NΠZ

⁽²⁾ Based on characterization, not actual test values.

⁽³⁾ Based on design, not actual test values.

⁽²⁾ Based on characterization, not actual test values.

⁽³⁾ Based on design, not actual test values.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DDIRC40K} ⁽³⁾	IRC40K oscillator operating current	V _{DD} =V _{DDA} =3.3V, T _A =25°C	_	0.41	_	μA
tsuirc40K ⁽³⁾	IRC40K oscillator startup time	V _{DD} =V _{DDA} =3.3V, T _A =25°C	_	33	_	μs

⁽¹⁾ V_{DD} = 3.3 V, T_A = -40 to 105 °C unless otherwise specified.

4.9 PLL characteristics

Table 4-21. PLL characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{PLLIN}	PLL input clock frequency		1 ⁽¹⁾	_	25	MHz
f _{PLLOUT}	PLL output clock frequency	_	16	_	72	MHz
t _{LOCK}	PLL lock time	_	_	_	300	μs
I _{DD} ⁽²⁾	Current consumption on V _{DD}	VCO freq=72MHz	_	130	_	μA
Jitter _{PLL} (3)	Cycle to cycle Jitter	System clock	_	300	_	ps

⁽¹⁾ Based on design, not actual test values.

4.10 Memory characteristics

Table 4-22. Flash memory characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
	Number of guaranteed					
PEcyc	program /erase cycles	T _A =-40°C ~ +85°C	100	_	_	kcycle
	before failure (Endurance)					
t _{RET}	Data retention time	10k cycles at T _A =85°C	10	_	_	year
t PROG	Word programming time	T _A =-40°C ~ +85°C	37	_	42	us
terase	Page erase time	T _A =-40°C ~ +85°C	0.8	_	1.1	ms
tmerase	Mass erase time	T _A =-40°C ~ +85°C	3.2	_	4	ms

⁽¹⁾ Based on characterization, not actual test values.

4.11 NRST pin characteristics

Table 4-23. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)}	NRST Input low level voltage	V _{DD} =V _{DDA} =1.8V	-0.5	_	0.71	V

⁽²⁾ Based on characterization, not actual test values.

⁽³⁾ Based on design, not actual test values.

⁽²⁾ Based on characterization, not actual test values.

⁽³⁾ Value given with main PLL running.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IH(NRST)} (1)	NRST Input high level voltage		1.08		V _{DD} +0.5	
V _{hyst}	Schmidt trigger Voltage hysteresis		_	370	_	mV
VIL(NRST) (1)	NRST Input low level voltage		-0.5	_	1.05	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
V _{IH(NRST)} (1)	NRST Input high level voltage	V _{DD} =V _{DDA} =2.5V	1.42	_	V _{DD} +0.5	V
V _{hyst}	Schmidt trigger Voltage hysteresis		_	370	_	mV
VIL(NRST) (1)	NRST Input low level voltage		-0.5	_	1.4	V
V _{IH(NRST)} (1)	NRST Input high level voltage	$V_{DD}=V_{DDA}=3.3V$	1.8	_	V _{DD} +0.5	V
V _{hyst}	Schmidt trigger Voltage hysteresis		_	400	_	mV
VIL(NRST) (1)	NRST Input low level voltage		-0.5	_	1.53	\/
V _{IH(NRST)} (1)	NRST Input high level voltage	V _{DD} =V _{DDA} =3.6V	1.95	_	V _{DD} +0.5	V
V _{hyst}	Schmidt trigger Voltage hysteresis		1	420	_	mV
R _{pu} ⁽²⁾	Pull-up equivalent resistor	_	-	40.3	_	ΚΩ

⁽¹⁾ Based on design, not actual test values.

4.12 **GPIO** characteristics

Table 4-24. I/O port DC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{DD} =1.8V		_	0.80	
	Standard IO Low level input	V _{DD} =2.5V	,	_	1.10	V
	voltage	V _{DD} =3.3V	Vss	_	1.40	V
\/		V _{DD} =3.6V		_	1.60	
V_{IL}		V _{DD} =1.8V		_	0.80	
	5V-tolerant IO Low level	V _{DD} =2.5V	\/	_	1.10	V
	input voltage	V _{DD} =3.3V	Vss	_	1.40	V
		V _{DD} =3.6V		_	1.60	
		V _{DD} =1.8V	1.10	_		
	Standard IO High level	V _{DD} =2.5V	1.50	_	\/	V
	input voltage	V _{DD} =3.3V	1.90	_	V _{DD}	V
V		V _{DD} =3.6V	2.00	_		
V _{IH}		V _{DD} =1.8V	1.10	_		
	5V-tolerant IO High level	V _{DD} =2.5V	1.50	_	,,	,,
	input voltage	V _{DD} =3.3V	1.90	_	V _{DD}	V
		V _{DD} =3.6V	2.00	_		
	Laveland automitualita na	V _{DD} =1.8V	_	_	0.20	
\ /	Low level output voltage	V _{DD} =2.5V	_	_	0.20	\/
Vol	for an IO Pin	V _{DD} =3.3V	_	_	0.10	V
	(I _{IO} = +8mA)	V _{DD} =3.6V	_	_	0.10	
1/	Low level output voltage	V _{DD} =1.8V	_	_	_	\/
Vol	for an IO Pin	V _{DD} =2.5V	_	_	0.50	V

⁽²⁾ Based on characterization, not actual test values.



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	$(I_{IO} = +20mA)$	V _{DD} =3.3V	_	_	0.40	
		V _{DD} =3.6V	_	_	0.40	
	High level output voltage VoH for an IO Pin (I _{IO} = +8mA)	V _{DD} =1.8V	1.50	_	_	
\/-··		V _{DD} =2.5V	2.30	_	_	V
VOH		V _{DD} =3.3V	3.10	_	_	V
		V _{DD} =3.6V	3.40	_	_	
	High level evitorit veltege	V _{DD} =1.8V	_	_	_	
Voh	High level output voltage for an IO Pin	V _{DD} =2.5V	1.90	_	_	V
VOH		V _{DD} =3.3V	2.80	_	_	V
	$(I_{10} = +20mA)$	V _{DD} =3.6V	3.10	_	_	
R _{PU}	Internal pull-up resistor		_	40	_	kΩ
R _{PD}	Internal pull-down resistor	_	_	40	_	kΩ

Table 4-25. I/O port AC characteristics(1) (2)

GPIOx_OSPD[1:0] bit value	Parameter	Conditions	Тур	Max	Unit	
	Marrianna	V _{DD} =1.8V, C _L =10pF	2	10		
0000 00000 0000 14 0	Maximum frequency ⁽³⁾	V _{DD} =1.8V, C _L =30pF	2	8	MHz	
GPIOx_OSPD0->OSPDy[1:0]	rrequency.	V _{DD} =1.8V, C _L =50pF	2	6		
=X0 (IO_Speed = 2MHz)	Output high/ low to	V _{DD} =1.8V, C _L =10pF	24.4/23.4	29.4/33.4		
(IO_Speed = Zivii iz)	low/ high level fall/	V _{DD} =1.8V, C _L =30pF	31.6/29.8	37.6/36.8	ns	
	rise time	V _{DD} =1.8V, C _L =50pF	49/43.2	51/42.2		
	Maximum	V _{DD} =1.8V, C _L =10pF	10	32		
	Maximum frequency ⁽³⁾	V _{DD} =1.8V, C _L =30pF	10	26	MHz	
GPIOx_OSPD0->OSPDy[1:0] =01	rrequency	V _{DD} =1.8V, C _L =50pF	10	18		
=01 (IO_Speed = 10MHz)	Output high/ low to	V _{DD} =1.8V, C _L =10pF	8.8/9.2	10.0/10.2		
(10_Speed = 10Mi12)	low/ high level fall/	V _{DD} =1.8V, C _L =30pF	12.0/12.8	12.0/11.0	ns	
	rise time	V _{DD} =1.8V, C _L =50pF	15/13.6	17.2/15.8		
	Maximum	V _{DD} =1.8V, C _L =10pF	_	20	MHz	
		V _{DD} =1.8V, C _L =30pF	50	54		
GPIOx_OSPD0->OSPDy[1:0] =11		V _{DD} =1.8V, C _L =50pF	_	40		
(IO_Speed = 50MHz)	Output high/ low to	V _{DD} =1.8V, C _L =10pF	_	3.6/3.2		
(10_opeeu = 301/11 12)	low/ high level fall/	V _{DD} =1.8V, C _L =30pF	8.0/5.0	7.4/4.0	ns	
	rise time	V _{DD} =1.8V, C _L =50pF	_	7.8/6.2		
	Maximum	V _{DD} =3.3V, C _L =10pF	2	16		
000 0000 0000 14 01	Maximum frequency ⁽³⁾	V _{DD} =3.3V, C _L =30pF	2	16	MHz	
GPIOx_OSPD0->OSPDy[1:0]	irequency.	V _{DD} =3.3V, C _L =50pF	2	12		
=X0	Output high/ low to	V _{DD} =3.3V, C _L =10pF	13.8/11.4	16.4/11.8		
(IO_Speed = 2MHz)	low/ high level fall/	V _{DD} =3.3V, C _L =30pF	19.0/14.8	19.2/17.8	ns	
	rise time	V _{DD} =3.3V, C _L =50pF	28.2/22.8	27.2/24.4		
GPIOx_OSPD0->OSPDy[1:0]	Maximum	V _{DD} =3.3V, C _L =10pF	10	72	N 41 :	
=01	frequency ⁽³⁾	V _{DD} =3.3V, C _L =30pF	10	72	MHz	



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ODOZEZOVA Datasne					,,,,,
GPIOx_OSPD[1:0] bit value	Parameter	Conditions	Тур	Max	Unit
(IO_Speed = 10MHz)		V _{DD} =3.3V, C _L =50pF	10	40	
	Output high/ low to	V _{DD} =3.3V, C _L =10pF	3.4/2.8	4.0/3.4	
	low/ high level fall/	V _{DD} =3.3V, C _L =30pF	4.6/3.4	5.2/4.0	ns
	rise time	V _{DD} =3.3V, C _L =50pF	8.0/6.4	8.2/6.2	
	Maximum	V _{DD} =3.3V, C _L =10pF	_	32	
CDION OCDDO COCDDNIA O	Maximum frequency ⁽³⁾	V _{DD} =3.3V, C _L =30pF	_	46	MHz
GPIOx_OSPD0->OSPDy[1:0]	rrequency(⁹ /	V _{DD} =3.3V, C _L =50pF	_	40	
=11 (IO_Speed = 50MHz)	Output high/ low to	V _{DD} =3.3V, C _L =10pF	_	2.4/2.6	
(10_Speed = 50Wil 12)	low/ high level fall/	V _{DD} =3.3V, C _L =30pF	_	2.6/2.4	ns
	rise time	V _{DD} =3.3V, C _L =50pF	_	8.4/3.2	
		V _{DD} =3.6V, C _L =10pF	2	16	
	Maximum	V _{DD} =3.6V, C _L =30pF	2	16	MHz
GPIOx_OSPD0->OSPDy[1:0] =X0 (IO_Speed = 2MHz)	frequency ⁽³⁾	V _{DD} =3.6V, C _L =50pF	2	12	
	Output high/ low to	V _{DD} =3.6V, C _L =10pF	13.2/10.6	12.0/10.4	
(10_Opeeu = 2ivii iz)	low/ high level fall/	V _{DD} =3.6V, C _L =30pF	17.2/14.4	18.8/15.4	ns
	rise time	V _{DD} =3.6V, C _L =50pF	26.8/22.2	26.4/21.8	
	Marrianna	V _{DD} =3.6V, C _L =10pF	10	72	
ODIO: OODDO OODD: [4:0]	Maximum	V _{DD} =3.6V, C _L =30pF	10	72	MHz
GPIOx_OSPD0->OSPDy[1:0] =01	frequency ⁽³⁾	V _{DD} =3.6V, C _L =50pF	10	40	
(IO_Speed = 10MHz)	Output high/ low to	V _{DD} =3.6V, C _L =10pF	3.2/2.8	3.6/3.2	
(10_Speed = 10Wil 12)	low/ high level fall/	V _{DD} =3.6V, C _L =30pF	3.8/3.2	4.4/3.4	ns
	rise time	V _{DD} =3.6V, C _L =50pF	7.6/6.0	8.0/6.0	
	Maximum	V _{DD} =3.6V, C _L =10pF	_	42	
CDIOV OCDDO - OCDDVI4-01	Maximum frequency ⁽³⁾	V _{DD} =3.6V, C _L =30pF	_	46	MHz
GPIOx_OSPD0->OSPDy[1:0]	irequericy/	V _{DD} =3.6V, C _L =50pF		36	
(IO_Speed = 50MHz)	=11 Output high/ low to		_	3.0/9.6	
10_opeeu = 50Wi 12)	low/ high level fall/	V _{DD} =3.6V, C _L =30pF	_	2.4/2.4	ns
	rise time	V _{DD} =3.6V, C _L =50pF	_	3.2/3.2	

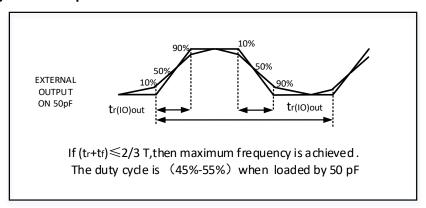
⁽¹⁾ Based on characterization, not actual test values.

⁽²⁾ The I/O speed is configured using the GPIOx_OSPD0->OSPDy [1:0] bits. Refer to the GD32E230xx user manual which is selected to set the GPIO port output speed.

⁽³⁾ The maximum frequency is defined in Figure 4-1. I/O port AC characteristics definition.



Figure 4-1. I/O port AC characteristics definition



4.13 ADC characteristics

Table 4-19. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DDA}	Operating voltage	_	2.4	3.3	3.6	V
VIN	ADC input voltage range	_	0	_	V _{REF+}	V
f _{ADC}	ADC clock	_	0.1	_	28	MHz
		12-bit	0.007	_	2	
fs ⁽¹⁾	Commingues	10-bit	0.008	_	2.3	MSP
IS(')	Sampling rate	8-bit	0.01	_	2.8	S
		6-bit	0.011	_	3.5	
V _{IN}	Analog input voltage	10 external;2 internal	0	_	V_{DDA}	V
V _{REF+}	Positive Reference Voltage	_	_	V _{DDA}	_	V
V _{REF} -	Negative Reference	_	_	0	_	V
R _{AIN} ⁽¹⁾	Voltage External input impedance	See Equation 2			50.6	kΩ
R _{ADC} ⁽¹⁾	Input sampling switch resistance	—	_	_	0.5	kΩ
C _{ADC} ⁽¹⁾	Input sampling capacitance	No pin/pad capacitance included	_	_	4	pF
tcal	Calibration time	f _{ADC} =28MHz	_	3.12		μs
ts	Sampling time	f _{ADC} =28MHz	0.05	_	8.55	μs
	Total assumation	12-bit	_	14	_	
4 (1)	Total conversion	10-bit	_	12	_	1/
t _{CONV} ⁽¹⁾	time(including sampling	8-bit	_	10	_	fadc
	time)	6-bit	_	8	_	
tsu ⁽¹⁾	Startup time		_	_	1	μs

⁽¹⁾ Based on characterization, not actual test values.

Equation 2: R_{AIN} max formula
$$R_{AIN} < \frac{T_s}{f_{ADC}*C_{ADC}*ln(2^{N+2})} - R_{ADC}$$



The formula above (Equation 2) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N=12 (from 12-bit resolution).

Table 4-20. ADC R_{AIN} max for $f_{ADC} = 28MHz^{(1)}$

T _s (cycles)	t _s (us)	R _{AINmax} (ΚΩ)
1.5	0.05	0.88
7.5	0.27	6.4
13.5	0.48	11.9
28.5	1.02	25.7
41.5	1.48	37.7
55.5	1.98	50.6
71.5	2.55	NA
239.5	8.55	NA

⁽¹⁾ Based on characterization, not actual test values.

4.14 Temperature sensor characteristics

Table 4-26. Temperature sensor characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T _L ⁽¹⁾	VSENSE linearity with temperature	_	±1.5	_	$^{\circ}\mathbb{C}$
Avg_Slope ⁽¹⁾	Average slope	_	4.3	_	mV/℃
V ₂₅ ⁽¹⁾	Voltage at 25 °C	_	1.45	_	V
t _{START}	Startup time	_	_	_	μs
t _{s_temp} (2) (3)	ADC sampling time when reading the temperature	_	17.1	_	μs

⁽¹⁾ Based on characterization, not actual test values.

4.15 Comparators characteristics

Table 4-27. CMP characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
V _{DDA}	Operating voltage	_	1.8	3.3	3.6	V
VIN	Input voltage range	_	0	_	V_{DDA}	٧
V _{BG}	Scaler input voltage	_	_	1.2	_	V
V _{SC}	Scaler offset voltage	_	_	_	_	mV
		Ultra-low power mode	_	0.98	_	μs
	Propagation delay for 200mv	Low power mode	_	0.25	_	μs
4_	step with 100mV overdrive	Medium power mode	_	0.12	_	μs
t₀		High speed power mode	_	33	_	ns
	Propagation delay for full	Ultra-low power mode	_	_	_	μs
	range step with 100mV	Low power mode	_	_	_	μs

⁽²⁾ Based on design, not actual test values.

⁽³⁾ Shortest sampling time can be determined in the application.



Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
	overdrive	Medium power mode	_	_		μs
		High speed power mode	_	_	_	ns
		Ultra-low power mode	_	2.2	_	
	Command as a summer diam	Low power mode	_	3.2	_	
I _{DD}	Current consumption	Medium power mode	_	8.1	_	μA
		High speed power mode	_	46.9	_	
Voffset	Offset error	_	_	±4	_	mV
		No Hysteresis	_	0	_	
.,	Lhustana da Maltana	Low Hysteresis	_	11	_	\/
V _{hyst}	Hysteresis Voltage	Medium Hysteresis	_	22	_	mV
		High Hysteresis	_	43	_	

⁽¹⁾ Based on characterization, not actual test values.

4.16 TIMER characteristics

Table 4-28. TIMER characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
	Timer resolution time	_	1	_	t _{TIMERxCLK}
t _{res}	Timer resolution time	f _{TIMERxCLK} = 72 MHz	13.9	_	ns
f EXT	Timer external clock	_	0	ftimerxclk/2	MHz
IEXI	frequency	f _{TIMERxCLK} = 72 MHz	0	36	MHz
RES	Timer resolution	_	_	16	bit
	16-bit counter clock period	_	1	65536	t _{TIMERxCLK}
tcounter	when internal clock is selected	f _{TIMERxCLK} = 72 MHz	0.0139	910	μs
thank count	Maximum possible count	_	_	65536 × 65536	t _{TIMERxCLK}
tmax_count	waxiinum possible count	f _{TIMERxCLK} = 72 MHz	_	59.6	S

4.17 WDGT characteristics

Table 4-29. FWDGT min/max timeout period at 40 kHz (IRC40K)

Prescaler divider	PR[2:0] bits	Min timeout RLD[11:0]= 0x000	Max timeout RLD[11:0]= 0xFFF	Unit
1/4	000	0.1	409.6	
1/8	001	0.2	819.2	
1/16	010	0.4	1638.4	
1/32	011	0.8	3276.8	ms
1/64	100	1.6	6553.6	
1/128	101	3.2	13107.2	
1/256	110 or 111	6.4	26214.4	



Table 4-30. WWDGT min-max timeout value @72 MHz (fPCLK1)

Prescaler divider	PSC[2:0]	Min timeout value CNT[6:0] = 0x40	Unit	Max timeout value CNT[6:0] = 0x7F	Unit
1/1	00	56.9		3.64	
1/2	01	113.8		7.28	
1/4	10	227.6	μs	14.56	ms
1/8	11	455.1		29.13	

4.18 I2C characteristics

Table 4-31. I2C characteristics

Cumbal	Parameter	Conditi	Standard	mode ⁽¹⁾	Fast mo	Unit	
Symbol	Parameter	ons	Min	Max	Min	Max	Unit
f _{SCL}	SCL clock frequency	_	0	100	0	1000	KHz
t _{SCL(H)}	SCL clock high time	_	4.0	_	0.6	_	μs
t _{SCL(L)}	SCL clock low time	_	4.7	_	1.3	_	μs
tsu(SDA)	SDA setup time	_	250	_	100	_	ns
th(SDA)	SDA data hold time	_	0(3)	3450	0	900	ns
tr(SDA/SCL)	SDA and SCL rise time	_	_	1000	_	300	ns
tf(SDA/SCL)	SDA and SCL fall time	_	_	300	_	300	ns
th(STA)	Start condition hold time	_	4.0	_	0.6	_	us

⁽¹⁾ Based on design, not actual test values.

4.19 SPI characteristics

Table 4-32. Standard SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fsck	SCK clock frequency	_		_	18	MHz
tsck(H)	SCK clock high time	_	25	27	29	ns
tsck(L)	SCK clock low time	_	25	27	29	ns
		SPI master mode				
t _{V(MO)}	Data output valid time	_	_	_	2	ns
tsu(MI)	Data input setup time		5		_	ns
t _{H(MI)}	Data input hold time	_	5	_	_	ns
		SPI slave mode				
t _{SU(NSS)}	NSS enable setup time	f _{PCLK} =72MHz	4T _{PCLK}	_	_	ns

⁽²⁾ To ensure the standard mode I2C frequency, f_{PCLK1} must be at least 2 MHz.To ensure the fast mode I2C frequency, f_{PCLK1} must be at least 4 MHz. To ensure the fast mode puls I2C frequency, f_{PCLK1} must be at least a multiple of 10 MHz.

⁽³⁾ The device should provide a data hold time of 300 ns at least in order to bridge the undefined region of the falling edge of SCL.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{H(NSS)}	NSS enable hold time	f _{PCLK} =72MHz	2T _{PCLK}	_		ns
t _{A(SO)}	Data output access time	f _{PCLK} =72MHz	2	_	55	ns
t _{DIS(SO)}	Data output disable time	_	3	_	10	ns
t _{V(SO)}	Data output valid time	_	_	_	29	ns
t _{SU(SI)}	Data input setup time	_	2	_	_	ns
t _{H(SI)}	Data input hold time	_	0			ns

⁽¹⁾ Data based on characterization results, not actual test values.

4.20 I2S characteristics

Table 4-33. I2S characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
		Master mode (data: 16 bits,			6		
fcĸ	Clock frequency	Audio frequency = 48 kHz)		_	0	MHz	
		Slave mode	_	_	6		
t _H	Clock high time	f CMIL-	_	_	83.33	ns	
t∟	Clock low time	f _{ск} =6МНz	_	_	83.33	ns	
tv(ws)	WS valid time	Master mode	0	_	2	ns	
t _{H(WS)}	WS hold time	Master mode	0	_	_	ns	
tsu(ws)	WS setup time	Slave mode	0	_	_	ns	
t _{H(WS)}	WS hold time	Slave mode	0.5	_	_	ns	
D. O.	I2S slave input clock duty	01 1	00		70	%	
DuCy(sck)	cycle	Slave mode	30	_	70	%	
tsu(SD_MR)	Data input setup time	Master mode	2	_	_	ns	
t _{su(SD_SR)}	Data input setup time	Slave mode	0	_	_	ns	
t _{H(SD_MR)}	Data is not bald time	Master receiver	1.5	_	_	ns	
t _{H(SD_SR)}	Data input hold time	Slave receiver	1.5	_	_	ns	
	Data autout valid ties a	Slave transmitter			44		
t _{v(SD_ST)}	Data output valid time	(after enable edge)		_	11	ns	
	Data autout hald time	Slave transmitter					
th(SD_ST)	Data output hold time	(after enable edge)	3	_	_	ns	
4	Data output valid time	Master transmitter			11	20	
t _{v(SD_MT)}	Data output valid time	(after enable edge)			11	ns	
t	Data output hold time	Master transmitter	0			no	
t _{h(SD_MT)}	Data output hold time	Data output hold time (after enable edge)		0	_	_	ns

⁽¹⁾ Data based on characterization results, not actual test values



4.21 USART characteristics

Table 4-34. USART characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fsck	SCK clock frequency		_	_	36	MHz
tsck(H)	SCK clock high time	_	13.5	_	_	ns
tsck(L)	SCK clock low time		13.5	_	_	ns

⁽¹⁾ Data based on characterization results, not actual test values.



5 Package information

5.1 TSSOP package outline dimensions

Figure 5-1. TSSOP package outline

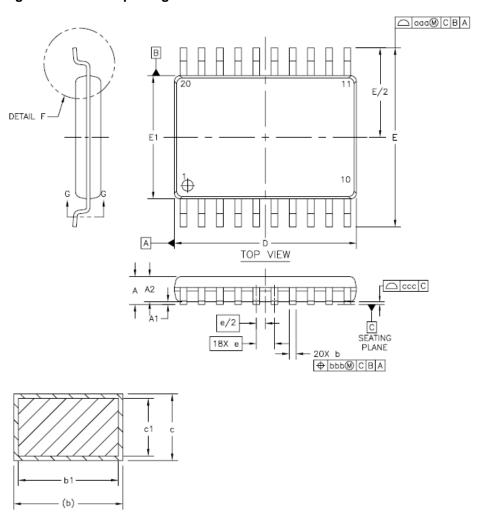


Table 5-1. TSSOP20 package dimensions

Cumbal	Dimensions (mm)			Cumbal	Dimensions (mm)		
Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
А	-	-	1.2	c1	0.09	-	0.16
A1	0.05	-	1.15	D	6.4	6.5	6.6
A2	0.80	1.00	1.05	E1	4.3	4.4	4.5
b	0.19	-	0.30	E	6.40		
B1	0.19	0.22	0.25	е	0.65		
С	0.09	-	0.20	L	0.45 0.6 0.75		0.75



5.2 QFN package outline dimensions

Figure 5-2. QFN package outline

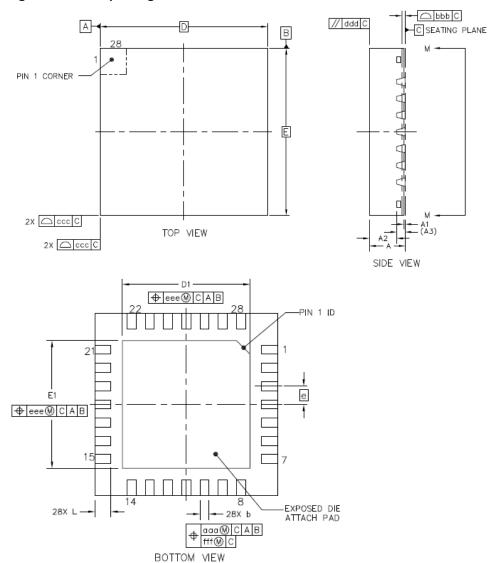




Table 5-2. QFN package dimensions

Symbol		QFN28		QFN32		
Symbol	Min		Max	Min	Тур	Max
Α	0.8	0.85	0.9	0.8	0.85	0.9
A1	0	0.035	0.05	0	0.035	0.05
A2	-	0.65	0.67	-	0.65	0.67
A3	-	0.203	-	-	0.203	-
D	-	4.0	-	-	5.0	-
E	-	4.0	-	-	5.0	-
D1	2.7	2.8	2.9	3.4	3.5	3.6
E1	2.7	2.8	2.9	3.4	3.5	3.6
L	0.25	0.35	0.45	0.3	0.4	0.5
е	0.4			0.5		
b	0.15	0.2	0.25	0.2	0.25	0.3

(Original dimensions are in millimeters)

Figure 5-3. QFN20 package outline

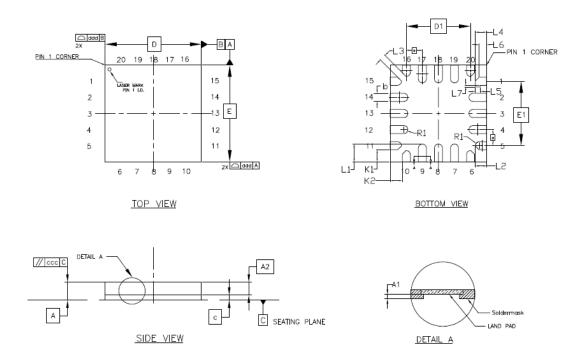




Table 5-3. QFN20 package dimensions

0	QFN20						
Symbol	Min	Тур	Max				
Α	0.51	0.56	0.61				
A1	-	0.015	0.022				
A2	0.35	0.40	0.45				
С	0.13	0.16	0.19				
D	2.90	3.00	3.10				
D1	1.95	2.00	2.05				
Е	2.90	3.00	3.10				
E1	1.95	2.00	2.05				
e	0.50 BASIC						
L1	0.50	0.55	0.60				
L2	0.30	0.35	0.40				
L3	0.200 REF						
L4	0.30 0.35		0.40				
L5	0.150 REF						
L6	0.234 REF						
L7	0.050 REF						
R1	0.125 REF						
K1	0.375 REF						
K2	0.375 REF						
b	0.20 0.25 0.30						
aaa	0.100						
ccc	0.100						

(Original dimensions are in millimeters)



5.3 LQFP package outline dimensions

Figure 5-4. LQFP package outline

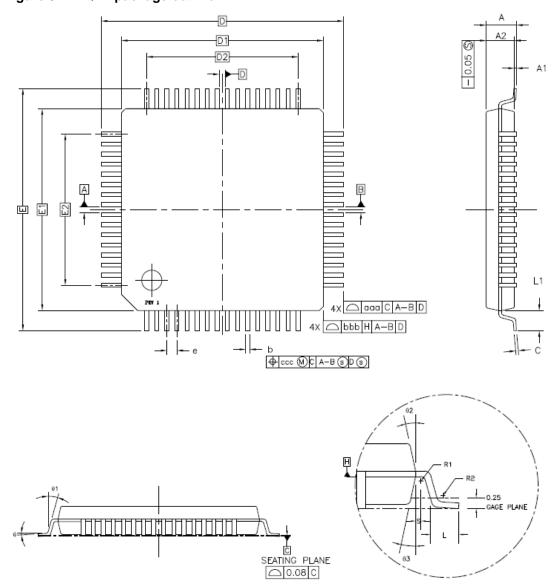




Table 5-4. LQFP package dimensions

Cumbal		LQFP32		LQFP48		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.60	-	-	1.50
A1	0.05	-	0.25	0.05	-	0.15
A2	1.35	1.40	1.45	0.95	1.00	1.35
D	-	9.00	-	-	9.00	-
D1	-	7.00	-	-	7.00	-
E	-	9.00	-	-	9.00	-
E1	-	7.00	-	-	7.00	-
R1	0.08	-	-	0.08	-	-
R2	0.08	-	0.20	0.08	-	0.20
θ	0°	3.5°	7°	0°	3.5°	7°
θ1	0°	-	-	0°	-	-
θ2	11°	12°	13°	11°	12°	13°
θ3	11°	12°	13°	11°	12°	13°
С	0.09	•	0.20	0.09	-	0.20
L	0.45	0.60	0.75	0.45	0.60	0.75
L1	-	1.00	-	-	1.00	-
S	0.20	•	-	0.20	-	-
b	0.17	0.22	0.27	0.17	0.22	0.27
е	-	0.50	-	-	0.50	-
D2	-	5.50	-	-	5.50	-
E2	-	5.50	-	-	5.50	-
aaa	0.20			0.20		
bbb	0.20			0.20		
ccc	0.08			0.08		

(Original dimensions are in millimeters)



6 Ordering information

Table 6-1. Part ordering code for GD32E230xx devices

Ordering code	Flash (KB)	Package	Package type	Temperature operating range
GD32E230F4U6	16	QFN20	Green	Industrial -40°C to +85°C
GD32E230F6U6	32	QFN20	Green	Industrial -40°C to +85°C
GD32E230F8U6	64	QFN20	Green	Industrial -40°C to +85°C
GD32E230F4P6	16	TSSOP20	Green	Industrial -40°C to +85°C
GD32E230F6P6	32	TSSOP20	Green	Industrial -40°C to +85°C
GD32E230F8P6	64	TSSOP20	Green	Industrial -40°C to +85°C
GD32E230G4U6	16	QFN28	Green	Industrial -40°C to +85°C
GD32E230G6U6	32	QFN28	Green	Industrial -40°C to +85°C
GD32E230G8U6	64	QFN28	Green	Industrial -40°C to +85°C
GD32E230K4U6	16	QFN32	Green	Industrial -40°C to +85°C
GD32E230K6U6	32	QFN32	Green	Industrial -40°C to +85°C
GD32E230K8U6	64	QFN32	Green	Industrial -40°C to +85°C
GD32E230K4T6	16	LQFP32	Green	Industrial -40°C to +85°C
GD32E230K6T6	32	LQFP32	Green	Industrial -40°C to +85°C
GD32E230K8T6	64	LQFP32	Green	Industrial -40°C to +85°C
GD32E230C4T6	16	LQFP48	Green	Industrial -40°C to +85°C
GD32E230C6T6	32	LQFP48	Green	Industrial -40°C to +85°C
GD32E230C8T6	64	LQFP48	Green	Industrial -40°C to +85°C



7 Revision history

Table 7-1. Revision history

Revision No.	Description	Date
1.0	Initial Release	Oct10, 2018
1.1	Add information about the QFN20 package	Dec7, 2018



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